Hiroshi Funakubo

List of Publications by Year
in descending order

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699 papers	12,506 citations	41258 49 h-index	56606 83 g-index
707 all docs	707 docs citations	707 times ranked	7564 citing authors

#	Article	IF	Citations
1	Dimensionality-Controlled Insulator-Metal Transition and Correlated Metallic State in<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mn>5</mml:mn><mml:mi>d</mml:mi></mml:math>Transition Metal Oxides<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mi>Sr</mml:mi><mml:mrow><mml:mi>n</mml:mi><mml:mo>+</mml:mo><mml:mn>1</mml:mn></mml:mr> mathvariant="norma. Physical Review Letters, 2008, 101, 226402.	2.9	425
2	Stabilizing the ferroelectric phase in doped hafnium oxide. Journal of Applied Physics, 2015, 118, .	1.1	424
3	Large remanent polarization of (Bi,Nd)4Ti3O12 epitaxial thin films grown by metalorganic chemical vapor deposition. Applied Physics Letters, 2002, 80, 2746-2748.	1.5	348
4	Crystal structure and ferroelectric properties of rare-earth substituted BiFeO3 thin films. Journal of Applied Physics, 2006, 100, 014106.	1.1	228
5	High-Î¤ Dielectric Nanofilms Fabricated from Titania Nanosheets. Advanced Materials, 2006, 18, 1023-1027.	11.1	206
6	The demonstration of significant ferroelectricity in epitaxial Y-doped HfO2 film. Scientific Reports, 2016, 6, 32931.	1.6	194
7	Impact of mechanical stress on ferroelectricity in (Hf0.5Zr0.5)O2 thin films. Applied Physics Letters, 2016, 108, .	1.5	187
8	Effect of cosubstitution of La and V in Bi4Ti3O12 thin films on the low-temperature deposition. Applied Physics Letters, 2002, 80, 100-102.	1.5	169
9	Cation Distribution and Structural Instability in Bi4-xLaxTi3O12. Japanese Journal of Applied Physics, 2001, 40, 5572-5575.	0.8	158
10	Approach for enhanced polarization of polycrystalline bismuth titanate films by Nd3+/V5+ cosubstitution. Applied Physics Letters, 2002, 81, 2229-2231.	1.5	157
11	Origin of giant negative piezoelectricity in a layered van der Waals ferroelectric. Science Advances, 2019, 5, eaav3780.	4.7	157
12	Robust High-Î¤ Response in Molecularly Thin Perovskite Nanosheets. ACS Nano, 2010, 4, 5225-5232.	7.3	141
13	Engineered Interfaces of Artificial Perovskite Oxide Superlattices via Nanosheet Deposition Process. ACS Nano, 2010, 4, 6673-6680.	7.3	141
14	Effects of deposition conditions on the ferroelectric properties of (Al1âˆ'xScx)N thin films. Journal of Applied Physics, 2020, 128, .	1.1	127
15	Growth of epitaxial orthorhombic YO1.5-substituted HfO2 thin film. Applied Physics Letters, 2015, 107, .	1.5	123
16	Dependence of electrical properties of epitaxial Pb(Zr,Ti)O3 thick films on crystal orientation and Zrâ•(Zr+Ti) ratio. Journal of Applied Physics, 2005, 98, 094106.	1.1	114
17	Epitaxial BiFeO3 thin films fabricated by chemical solution deposition. Applied Physics Letters, 2006, 88, 162904.	1.5	114
18	Preparation and characterization of a- and b-axis-oriented epitaxially grown Bi4Ti3O12-based thin films with long-range lattice matching. Applied Physics Letters, 2002, 81, 1660-1662.	1.5	101

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19	Rhombohedralâ€“Tetragonal Phase Boundary with High Curie Temperature in (1-x)BiCoO₃â€“xBiFeO₃ Solid Solution. Japanese Journal of Applied Physics, 2008, 47, 7579.	0.8	95
20	Large remanent polarization of Bi4Ti3O12-based thin films modified by the site engineering technique. Journal of Applied Physics, 2002, 92, 1518-1521.	1.1	92
21	Highly-conducting indiumî—¸tin-oxide transparent films fabricated by spray CVD using ethanol solution of indium (III) chloride and tin (II) chloride. Thin Solid Films, 2002, 409, 46-50.	0.8	91
22	Ion Modification for Improvement of Insulating and Ferroelectric Properties of BiFeO3Thin Films Fabricated by Chemical Solution Deposition. Japanese Journal of Applied Physics, 2005, 44, L561-L563.	0.8	89
23	Electrical properties of (001)- and (116)-oriented epitaxial SrBi2Ta2O9 thin films prepared by metalorganic chemical vapor deposition. Applied Physics Letters, 1999, 75, 1970-1972.	1.5	87
24	Improvement of Property of Pb(ZrxTi1-x)O3 Thin Film Prepared by Source Gas Pulse-Introduced Metalorganic Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2000, 39, L996-L998.	0.8	85
25	Controlled crystal growth of layered-perovskite thin films as an approach to study their basic properties. Journal of Applied Physics, 2006, 100, 051602.	1.1	84
26	Bi3-xMxTiTaO9(M = La or Nd) Ceramics with High Mechanical Quality FactorQm. Japanese Journal of Applied Physics, 2003, 42, 6090-6093.	0.8	79
27	Structural Characterization of BiFeO3Thin Films by Reciprocal Space Mapping. Japanese Journal of Applied Physics, 2006, 45, 7311-7314.	0.8	77
28	Film thickness dependence of ferroelectric properties of c-axis-oriented epitaxial Bi4Ti3O12 thin films prepared by metalorganic chemical vapor deposition. Journal of Applied Physics, 2001, 89, 3934-3938.	1.1	75
29	Large remanent polarization of 100% polar-axis-oriented epitaxial tetragonal Pb(Zr0.35Ti0.65)O3 thin films. Applied Physics Letters, 2003, 82, 4761-4763.	1.5	72
30	Controlled Polarizability of Oneâ€Nanometerâ€Thick Oxide Nanosheets for Tailored, Highâ€Î° Nanodielectrics. Advanced Functional Materials, 2011, 21, 3482-3487.	7.8	72
31	Composition and orientation dependence of electrical properties of epitaxial Pb(ZrxTi1â^'x)O3 thin films grown using metalorganic chemical vapor deposition. Journal of Applied Physics, 2004, 95, 3111-3115.	1.1	71
32	Ferroelectricity mediated by ferroelastic domain switching in HfO2-based epitaxial thin films. Applied Physics Letters, 2018, 113, .	1.5	69
33	Structural characterization and 90Â° domain contribution to ferroelectricity of epitaxial Pb(Zr0.35,Ti0.65)O3 thin films. Journal of Applied Physics, 2003, 93, 545-550.	1.1	68
34	Contribution of oxygen vacancies to the ferroelectric behavior of Hf0.5Zr0.5O2 thin films. Applied Physics Letters, 2015, 106, .	1.5	65
35	Spontaneous polarization change with Zrâ^•(Zr+Ti) ratios in perfectly polar-axis-orientated epitaxial tetragonal Pb(Zr,Ti)O3 films. Applied Physics Letters, 2004, 85, 3516-3518.	1.5	64
36	Low-Temperature Deposition of SrRuO3Thin Film Prepared by Metalorganic Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2000, 39, 572-576.	0.8	62

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37	Growth of (111)-oriented epitaxial and textured ferroelectric Y-doped HfO2 films for downscaled devices. Applied Physics Letters, 2016, 109, .	1.5	62
38	Method of Distinguishing SrBi2Ta2O9Phase from Fluorite Phase Using X-Ray Diffraction Reciprocal Space Mapping. Japanese Journal of Applied Physics, 2000, 39, 5489-5495.	0.8	61
39	Fabrication of M3+-Substituted and M3+/V5+-Cosubstituted Bismuth Titanate Thin Films [M=lanthanoid] by Chemical Solution Deposition Technique. Japanese Journal of Applied Physics, 2002, 41, 6820-6824.	0.8	61
40	Analysis for crystal structure of Bi(Fe,Sc)O3 thin films and their electrical properties. Applied Physics Letters, 2007, 91, .	1.5	60
41	Film Thickness Dependence of Dielectric Property and Crystal Structure of PbTiO3Film Prepared on Pt/SiO2/Si Substrate by Metal Organic Chemical Vapor Deposition. Japanese Journal of Applied Physics, 1993, 32, 4175-4178.	0.8	57
42	Orientation control and domain structure analysis of {100}-oriented epitaxial ferroelectric orthorhombic HfO2-based thin films. Journal of Applied Physics, 2016, 119, .	1.1	57
43	Ferroelectric properties of lanthanide-substituted Bi4Ti3O12 epitaxial thin films grown by metalorganic chemical vapor deposition. Journal of Applied Physics, 2003, 93, 1707-1712.	1.1	55
44	Orientation dependence of ferroelectricity of epitaxially grown Pb(ZrxTi1â˜'x)O3 thin films prepared by metalorganic chemical vapor deposition. Journal of Applied Physics, 2001, 89, 4517-4522.	1.1	53
45	Ferroelectricity in YO1.5-HfO2 films around 1â€‰Î¼m in thickness. Applied Physics Letters, 2019, 115, .	1.5	53
46	Composition Control of Pb(ZrxTi1-x)O3Thin Films Prepared by Metalorganic Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2000, 39, 212-216.	0.8	52
47	Ferroelectric properties of an epitaxial lead zirconate titanate thin film deposited by a hydrothermal method below the Curie temperature. Applied Physics Letters, 2004, 84, 5094-5096.	1.5	52
48	Crystal Structure and Electrical Properties of Epitaxial BiFeO3Thin Films Grown by Metal Organic Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2005, 44, L1231-L1233.	0.8	52
49	Charge trapping-detrapping induced resistive switching in Ba0.7Sr0.3TiO3. AIP Advances, 2012, 2, .	0.6	50
50	Dependence of Ferroelectric Properties on Thickness of BiFeO3Thin Films Fabricated by Chemical Solution Deposition. Japanese Journal of Applied Physics, 2005, 44, 8525-8527.	0.8	49
51	Ferroelectric property of epitaxial Bi₄Ti₃O₁₂ films prepared by metalorganic chemical vapor deposition. Journal of Materials Research, 2001, 16, 303-307.	1.2	48
52	Ruthenium Film with High Nuclear Density Deposited by MOCVD Using a Novel Liquid Precursor. Electrochemical and Solid-State Letters, 2003, 6, C117.	2.2	48
53	Crystal Structure Analysis of Epitaxial BiFeO3â€"BiCoO3Solid Solution Films Grown by Metalorganic Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2007, 46, 6948-6951.	0.8	48
54	Thickness-dependent crystal structure and electric properties of epitaxial ferroelectric Y2O3-HfO2 films. Applied Physics Letters, 2018, 113, .	1.5	48

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55	Epitaxial PZT films for MEMS printing applications. MRS Bulletin, 2012, 37, 1030-1038.	1.7	47
56	Effect of Strain in Epitaxially Grown SrRuO3Thin Films on Crystal Structure and Electric Properties. Japanese Journal of Applied Physics, 2002, 41, 5376-5380.	0.8	45
57	Site definition and characterization of La-substituted Bi4Ti3O12 thin films prepared by metalorganic chemical vapor deposition. Journal of Applied Physics, 2001, 90, 6533-6535.	1.1	43
58	Epitaxial-grade polycrystalline Pb(Zr,Ti)O3 film deposited at low temperature by pulsed-metalorganic chemical vapor deposition. Applied Physics Letters, 2001, 79, 1000-1002.	1.5	43
59	Domain distributions in tetragonal Pb(Zr,Ti)O3 thin films probed by polarized Raman spectroscopy. Applied Physics Letters, 2005, 87, 232902.	1.5	43
60	Fabrication of ZnO Microstructures by Anisotropic Wet-Chemical Etching. Journal of the Electrochemical Society, 2007, 154, D82.	1.3	43
61	Effect of the thermal expansion matching on the dielectric tunability of (100)-one-axis-oriented (Ba0.5Sr0.5)TiO3 thin films. Applied Physics Letters, 2007, 90, 142910.	1.5	42
62	Configuration and local elastic interaction of ferroelectric domains and misfit dislocation in PbTiO₃/SrTiO₃epitaxial thin films. Science and Technology of Advanced Materials, 2011, 12, 034413.	2.8	41
63	Effect of the film thickness on the crystal structure and ferroelectric properties of (Hf 0.5 Zr 0.5)O 2 thin films deposited on various substrates. Materials Science in Semiconductor Processing, 2017, 70, 239-245.	1.9	41
64	Growth of Î²-FeSi2 Thin Film on Si (111) by Metal-Organic Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2001, 40, L460-L462.	0.8	40
65	Room-temperature epitaxial growth of indium tin oxide thin films on Si substrates with an epitaxial CeO2 ultrathin buffer. Thin Solid Films, 2002, 415, 272-275.	0.8	40
66	Fatigue-free RuO2/Pb(Zr,Ti)O3/RuO2 capacitor prepared by metalorganic chemical vapor deposition at 395â€ŠÂ°C. Applied Physics Letters, 2003, 83, 5506-5508.	1.5	40
67	RF Magnetron Sputtering Growth of Epitaxial SrRuO₃ Films with High Conductivity. Japanese Journal of Applied Physics, 2007, 46, 6987.	0.8	40
68	Crystal Structure and Electrical Properties of {100}-Oriented Epitaxial BiCoO₃â€“BiFeO₃ Films Grown by Metalorganic Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2008, 47, 7582.	0.8	40
69	Transport properties and c/a ratio of V2O3 thin films grown on C- and R-plane sapphire substrates by pulsed laser deposition. Applied Physics Letters, 2015, 107, .	1.5	40
70	Large piezoelectric response in (111)-oriented epitaxial Pb(Zr,Ti)O3 films consisting of mixed phases with rhombohedral and tetragonal symmetry. Applied Physics Letters, 2003, 83, 2408-2410.	1.5	39
71	Thickness dependence of dielectric properties in bismuth layer-structured dielectrics. Applied Physics Letters, 2006, 89, 082901.	1.5	39
72	Y2O3-Stabilized ZrO2Thin Films Prepared by Metalorganic Chemical Vapor Deposition. Japanese Journal of Applied Physics, 1998, 37, 6229-6232.	0.8	38

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73	(111)-textured Mn-substituted BiFeO3 thin films on SrRuO3âˆ•Ptâˆ•Tiâˆ•SiO2âˆ•Si structures. Applied Physics Letters, 2007, 90, 242914.	1.5	38
74	Crystal structure and electrical properties of epitaxial SrBi2Ta2O9 films. Journal of Applied Physics, 2000, 87, 8018-8023.	1.1	37
75	Laser Wavelength Effect on Size and Morphology of Silicon Nanoparticles Prepared by Laser Ablation in Liquid. Japanese Journal of Applied Physics, 2013, 52, 025001.	0.8	37
76	Experimental discovery of structureâ€“property relationships in ferroelectric materials via active learning. Nature Machine Intelligence, 2022, 4, 341-350.	8.3	37
77	Crystal structure, electrical properties, and mechanical response of (100)-/(001)-oriented epitaxial Pb(Mg1âˆ•3Nb2âˆ•3)O3â€“PbTiO3 films grown on (100)cSrRuO3â€–(100)SrTiO3 substrates by metal-organic chemical vapor deposition. Journal of Applied Physics, 2006, 100, 054110.	1.1	36
78	Property design of Bi4Ti3O12-based thin films using a site-engineered concept. Journal of Crystal Growth, 2003, 248, 180-185.	0.7	35
79	The Influence of Acceptor Doping on the Structure and Electrical Properties of Sol-Gel Derived BiFeO₃Thin Films. Ferroelectrics, 2007, 357, 35-40.	0.3	35
80	Enhancement of ferroelectric and magnetic properties in BiFeO3 films by small amount of cobalt addition. Journal of Applied Physics, 2008, 103, .	1.1	35
81	Electrical properties of semiconductive Nb-doped BaTiO3 thin films prepared by metalâ€“organic chemical-vapor deposition. Applied Physics Letters, 1998, 72, 2017-2019.	1.5	34
82	Orientation Control of ZnO Thin Film Prepared by CVD. , 1999, 4, 25-32.		34
83	Preparation of Pb(Zrx, Ti1-x)O3Thin Films by Source Gas Pulse-Introduced Metalorganic Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2001, 40, 4126-4130.	0.8	34
84	Modulation derived satellite peaks in x-ray reciprocal mapping on bismuth cuprate superconductor film. Applied Physics Letters, 2004, 85, 2301-2303.	1.5	34
85	Effects of heat treatment and in situ high-temperature X-ray diffraction study on the formation of ferroelectric epitaxial Y-doped HfO₂ film. Japanese Journal of Applied Physics, 2019, 58, SBBB09.	0.8	34
86	Metalorganic Chemical Vapor Deposition of Epitaxial Perovskite SrIrO3Films on (100)SrTiO3Substrates. Japanese Journal of Applied Physics, 2006, 45, L36-L38.	0.8	33
87	Strain-relaxed structure in (001)âˆ•(100)-oriented epitaxial PbTiO3 films grown on (100) SrTiO3 substrates by metal organic chemical vapor deposition. Applied Physics Letters, 2007, 91, .	1.5	33
88	Suppressed polar distortion with enhanced Curie temperature in in-plane 90Â°-domain structure of a-axis oriented PbTiO3 Film. Applied Physics Letters, 2015, 106, .	1.5	33
89	Ferroelectric property of an epitaxial lead zirconate titanate thin film deposited by a hydrothermal method. Journal of Materials Research, 2004, 19, 1862-1868.	1.2	32
90	Structural modulation on multilayered bismuth cuprate observed by x-ray reciprocal space mapping. Journal of Applied Physics, 2005, 97, 103904.	1.1	32

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91	Comprehensive Study on the Kinetic Formation of the Orthorhombic Ferroelectric Phase in Epitaxial Y-Doped Ferroelectric HfO₂ Thin Films. ACS Applied Electronic Materials, 2021, 3, 3123-3130.	2.0	32
92	Metal organic chemical vapor deposition growth of epitaxial SrRuO3 and CaRuO3 thin films with different orientations as the bottom electrode for epitaxial ferroelectric thin film. Journal of Crystal Growth, 2002, 235, 401-406.	0.7	31
93	Evaluation of oxygen vacancies in ZnO single crystals and powders by micro-Raman spectroscopy. Journal of the Ceramic Society of Japan, 2017, 125, 445-448.	0.5	31
94	Strain-amplified structural modulation of Bi-cuprate high-Tcsuperconductors. Physical Review B, 2006, 74, .	1.1	30
95	Langmuirâ€“Blodgett Fabrication of Nanosheet-Based Dielectric Films without an Interfacial Dead Layer. Japanese Journal of Applied Physics, 2008, 47, 7556.	0.8	30
96	Thick Epitaxial Pb(Zr_{0.35},Ti_{0.65})O₃Films Grown on (100)CaF₂Substrates with Polar-Axis-Orientation. Applied Physics Express, 0, 1, 085001.	1.1	30
97	Formation of the orthorhombic phase in CeO2-HfO2 solid solution epitaxial thin films and their ferroelectric properties. Applied Physics Letters, 2019, 114, .	1.5	30
98	Thickness scaling of (Al_{0.8}Sc_{0.2})N films with remanent polarization beyond 100ÂÎ¼CÂcm^{â^'2} around 10Ânm in thickness. Applied Physics Express, 2021, 14, 105501.	1.1	30
99	Effect of La substitution on Electrical Properties of Highly Oriented Bi4Ti3O12Films Prepared by Metalorganic Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2003, 42, 166-169.	0.8	29
100	Domain structures and piezoelectric properties in epitaxial Pb(Zr0.35,Ti0.65)O3 thin films. Applied Physics Letters, 2006, 88, 252904.	1.5	29
101	Dynamic piezoresponse force microscopy: Spatially resolved probing of polarization dynamics in time and voltage domains. Journal of Applied Physics, 2012, 112, .	1.1	29
102	Formation of (111) orientation-controlled ferroelectric orthorhombic HfO2 thin films from solid phase via annealing. Applied Physics Letters, 2016, 109, .	1.5	29
103	Orientation Dependence of Epitaxial and One-Axis-Oriented (Ba0.5Sr0.5)TiO3Films Prepared by RF Magnetron Sputtering. Japanese Journal of Applied Physics, 2005, 44, 6881-6884.	0.8	28
104	Domain structure of (100)/(001)-oriented epitaxial PbTiO3 thick films with various volume fraction of (001) orientation grown by metal organic chemical vapor deposition. Applied Physics Letters, 2009, 94, .	1.5	28
105	Measurement of transient photoabsorption and photocurrent of BiFeO<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:msub><mml:mrow /><mml:mn>3</mml:mn></mml:msub></mml:math>thin films: Evidence for long-lived trapped photocarriers. Physical Review B, 2014, 89, .	1.1	28
106	Room-temperature deposition of ferroelectric HfO2-based films by the sputtering method. Applied Physics Letters, 2020, 116, .	1.5	28
107	Preparation of SrBi2Ta2O9 Thin Films by Metalorganic Chemical Vapor Deposition from Two New Liquid Organometallic Sources. Japanese Journal of Applied Physics, 1999, 38, L199-L201.	0.8	27
108	Orientation Control of Metalorganic Chemical Vapor Deposition-Bi4Ti3O12Thin Film by Sequential Source Gas Supply Method. Japanese Journal of Applied Physics, 2000, 39, 5211-5216.	0.8	27

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109	Low Temperature Deposition of Pb(Zr,Ti)O3 Film by Source Gas Pulse-Introduced Metalorganic Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2001, 40, L343-L345.	0.8	27
110	Growth of Epitaxial Î²-FeSi2Thin Film on Si(001) by Metal-Organic Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2004, 43, L551-L553.	0.8	27
111	Phase Diagram and Microstructure in the ZnOâ€“Pr₂O₃ System. Journal of the American Ceramic Society, 1997, 80, 995-998.	1.9	27
112	Seed Layer Free Conformal Ruthenium Film Deposition on Hole Substrates by MOCVD Using (2,4-Dimethylpentadienyl)(ethylcyclopentadienyl)ruthenium. Electrochemical and Solid-State Letters, 2006, 9, C107.	2.2	27
113	Low-Temperature Preparation of Metallic Ruthenium Films by MOCVD Using Bis(2,4-dimethylpentadienyl)ruthenium. Electrochemical and Solid-State Letters, 2007, 10, D60.	2.2	27
114	Residual Strain and Crystal Structure ofBaTiO3â€“SrTiO3Thin Films Prepared by Metal Organic Chemical Vapor Deposition. Japanese Journal of Applied Physics, 1997, 36, 5879-5884.	0.8	26
115	Effect of Deposition Temperature and Composition on the Microstructure and Electrical Property of SrBi2Ta2O9Thin Films Prepared by Metalorganic Chemical Vapor Deposition. Japanese Journal of Applied Physics, 1999, 38, 5428-5431.	0.8	26
116	Crystal Orientation Dependence on Electrical Properties of Pb(Zr,Ti)O3Thick Films Grown on Si Substrates by Metalorganic Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2004, 43, 6567-6570.	0.8	26
117	The effects of neodymium content and site occupancy on spontaneous polarization of epitaxial (Bi4â^'xNdx)Ti3O12 films. Journal of Applied Physics, 2005, 98, 024110.	1.1	26
118	Experimental evidence for orientation property of Pb(Zr0.35Ti0.65)O3 by manipulating polar axis angle using CaF2 substrate. Applied Physics Letters, 2010, 96, 102905.	1.5	26
119	Growth of Epitaxial 100-Oriented KNbO$_{3}$â€“NaNbO$_{3}$ Solid Solution Films on (100)$_{ext{c}}$SrRuO$_{3}$$$parallel$(100)SrTiO$_{3}$ by Hydrothermal Method and Their Characterization. Japanese Journal of Applied Physics, 2011, 50, 09ND11.	0.8	26
120	Dependence of e31,f on polar axis texture for tetragonal Pb(Zrx,Ti1â^'x)O3 thin films. Journal of Applied Physics, 2014, 116, .	1.1	26
121	Preparation and characterization of Pb(Nb,Ti)O3 thin films by metalorganic chemical vapor deposition. Journal of Applied Physics, 1999, 86, 4559-4564.	1.1	25
122	Preparation of bismuth layer-structured ferroelectric thin films by MOCVD and their characterization. Advanced Materials for Optics and Electronics, 2000, 10, 193-200.	0.6	25
123	Epitaxial Pt Films with Different Orientations Grown on (100)Si Substrates by RF Magnetron Sputtering. Japanese Journal of Applied Physics, 2005, 44, 5102-5106.	0.8	25
124	Large constriction of lattice constant in epitaxial magnesium oxide thin film: Effect of point defects on lattice constant. Journal of Applied Physics, 2010, 107, 073523.	1.1	25
125	Impact of thermal expansion of substrates on phase transition temperature of VO2 films. Journal of Applied Physics, 2014, 116, 123510.	1.1	25
126	Impact of pulse poling on static and dynamic ferroelastic-domain contributions in tetragonal Pb(Ti,) Tj ETQq0 0 0 rgBT /Overlock 10 Tf 5 .	1.1	25

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127	Electrical Properties of (110)-Oriented Nondoped Mg2Si Films with p-Type Conduction Prepared by RF Magnetron Sputtering Method. Journal of Electronic Materials, 2014, 43, 2269-2273.	1.0	25
128	Metalorganic Chemical Vapor Deposition of Conductive CaRuO3Thin Films. Japanese Journal of Applied Physics, 2000, 39, 2780-2783.	0.8	24
129	Thickness scaling of polycrystalline Pb(Zr,Ti)O3 films downto 35nm prepared by metalorganic chemical vapor depositionhaving good ferroelectric properties. Applied Physics Letters, 2004, 85, 1754-1756.	1.5	24
130	Domain structure control of (001)âˆ•(100)-oriented epitaxial Pb(Zr,Ti)O3 films grown on (100)cSrRuO3âˆ•(100)SrTiO3 substrates. Applied Physics Letters, 2005, 86, 212905.	1.5	24
131	Evaluation of Residual Strain and Oxygen Vacancy in Multilayer Ceramic Capacitor Using Laser Raman Spectroscopy. Japanese Journal of Applied Physics, 2007, 46, 7005.	0.8	24
132	Strong growth orientation dependence of strain relaxation in epitaxial (Ba,Sr)TiO3 films and the resulting dielectric properties. Journal of Applied Physics, 2011, 109, .	1.1	24
133	Real-space mapping of dynamic phenomena during hysteresis loop measurements: Dynamic switching spectroscopy piezoresponse force microscopy. Applied Physics Letters, 2011, 98, 202903.	1.5	24
134	Direct observation of intrinsic piezoelectricity of Pb(Zr,Ti)O3 by time-resolved x-ray diffraction measurement using single-crystalline films. Applied Physics Letters, 2014, 105, .	1.5	24
135	Crystal structure and dielectric/ferroelectric properties of CSD-derived HfO 2 -ZrO 2 solid solution films. Ceramics International, 2017, 43, S501-S505.	2.3	24
136	Preparation of Bi2WO6 thin films by metalorganic chemical vapor deposition and their electrical properties. Thin Solid Films, 2001, 392, 128-133.	0.8	23
137	Photoluminescence Properties from Î²-FeSi2Film Epitaxially Grown on Si, YSZ and Si//YSZ. Japanese Journal of Applied Physics, 2005, 44, L303-L305.	0.8	23
138	1.54 Î¼m photoluminescence from Î²-FeSi2 as-deposited film. Applied Physics Letters, 2007, 91, .	1.5	23
139	Step coverage study of indium-tin-oxide thin films by spray CVD on non-flat substrates at different temperatures. Thin Solid Films, 2008, 516, 5864-5867.	0.8	23
140	Crystal structure and electrical property comparisons of epitaxial Pb(Zr,Ti)O3 thick films grown on (100)CaF2 and (100)SrTiO3 substrates. Journal of Applied Physics, 2009, 105, 061614.	1.1	23
141	Spontaneous polarization estimation from the soft mode in strain-free epitaxial polar axis-oriented Pb(Zr,Ti)O3 thick films with tetragonal symmetry. Applied Physics Letters, 2011, 98, .	1.5	23
142	Effects of the porous structures in the porous flow field type separators on fuel cell performances. International Journal of Hydrogen Energy, 2014, 39, 15072-15080.	3.8	23
143	Photocatalytic hydrogen evolution over Î²-iron silicide under infrared-light irradiation. Chemical Communications, 2015, 51, 2818-2820.	2.2	23
144	In-situ observation of ultrafast 90Â° domain switching under application of an electric field in (100)/(001)-oriented tetragonal epitaxial Pb(Zr0.4Ti0.6)O3 thin films. Scientific Reports, 2017, 7, 9641.	1.6	23

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145	Fabrication of ferroelectric Fe doped HfO₂ epitaxial thin films by ion-beam sputtering method and their characterization. Japanese Journal of Applied Physics, 2018, 57, 11UF02.	0.8	23
146	Electricâ€Fieldâ€Induced Ferroelectricity in 5%Yâ€doped Hf_{0.5}Zr_{0.5}O₂: Transformation from the Paraelectric Tetragonal Phase to the Ferroelectric Orthorhombic Phase. Physica Status Solidi - Rapid Research Letters, 2021, 15, 2000589.	1.2	23
147	Autonomous Experiments in Scanning Probe Microscopy and Spectroscopy: Choosing Where to Explore Polarization Dynamics in Ferroelectrics. ACS Nano, 2021, 15, 11253-11262.	7.3	23
148	Effect of Film Microstructure on Domain Nucleation and Intrinsic Switching in Ferroelectric Y:HfO₂ Thin Film Capacitors. Advanced Functional Materials, 2022, 32, 2108876.	7.8	23
149	Spontaneous Polarization of Neodymium-Substituted Bi4Ti3O12Estimated from Epitaxially Grown Thin Films with in-Planec-Axis Orientations. Japanese Journal of Applied Physics, 2004, 43, L309-L311.	0.8	22
150	MOCVD growth of epitaxial SrIrO3 films on (111)SrTiO3 substrates. Thin Solid Films, 2005, 486, 182-185.	0.8	22
151	Electronic and Structural Properties of ABO3: Role of the B-O Coulomb Repulsions for Ferroelectricity. Materials, 2011, 4, 260-273.	1.3	22
152	Crystal Structure Analysis of Hydrothermally Synthesized Epitaxial (K_xNa_{1-x})NbO₃ Films. Japanese Journal of Applied Physics, 2013, 52, 09KA11.	0.8	22
153	Crystallization behavior and ferroelectric property of HfO₂â€“ZrO₂ films fabricated by chemical solution deposition. Japanese Journal of Applied Physics, 2018, 57, 11UF06.	0.8	22
154	Thickness- and orientation- dependences of Curie temperature in ferroelectric epitaxial Y doped HfO₂ films. Japanese Journal of Applied Physics, 2020, 59, SGGB04.	0.8	22
155	Formation of Epitaxial Pb(Zr, Ti)O₃ Film by CVD. Journal of the Ceramic Society of Japan, 1991, 99, 248-250.	1.3	21
156	Role of Non-180Â° Domain Switching in Electrical Properties of Pb(Zr0.35, Ti0.65)O3Thin Films. Japanese Journal of Applied Physics, 2002, 41, 6730-6734.	0.8	21
157	Micro-patterning of ZnO single crystal surface by anisotropic wet-chemical etching. Thin Solid Films, 2005, 486, 42-45.	0.8	21
158	Probing intrinsic polarization properties in bismuth-layered ferroelectric films. Applied Physics Letters, 2007, 90, 112914.	1.5	21
159	Effect of Oxygen Annealing on Ferroelectricity of BiFeO3Thin Films Formed by Pulsed Laser Deposition. Japanese Journal of Applied Physics, 2007, 46, 3491-3494.	0.8	21
160	Ultrafast switching of ferroelastic nanodomains in bilayered ferroelectric thin films. Applied Physics Letters, 2011, 99, 182906.	1.5	21
161	Improved ferroelectric property of very thin Mn-doped BiFeO3 films by an inlaid Al2O3 tunnel switch. Journal of Applied Physics, 2011, 110, 074111.	1.1	21
162	Composition dependency of crystal structure, electrical and piezoelectric properties for hydrothermally-synthesized 3 Âµm-thickness (K<i>_x</i>Na_{1â^'}<i>_x</i>)NbO<sub>3& films. Journal of the Ceramic Society of Japan, 2013, 121, 627-631.	0.5	21

#	Article	IF	Citations
163	Negligible substrate clamping effect on piezoelectric response in (111)-epitaxial tetragonal Pb(Zr, Ti)O3 films. Journal of Applied Physics, 2015, 118, .	1.1	21
164	Local Epitaxial Growth of (103) One-Axis-Oriented SrBi2Ta2O9Thin Films Prepared at Low Deposition Temperature by Metalorganic Chemical Vapor Deposition and Their Electrical Properties. Japanese Journal of Applied Physics, 2001, 40, 5595-5598.	0.8	20
165	Preparation of Orientation-Controlled Polycrystalline Pb(Zr, Ti)O3Thick Films on (100)Si Substrates by Metalorganic Chemical Vapor Deposition and Their Electrical Properties. Japanese Journal of Applied Physics, 2002, 41, 6705-6708.	0.8	20
166	Composition dependence of ferroelectric properties of epitaxial Pb(ZrxTi1â^'x)O3 thin films grown by metalorganic chemical vapor deposition. Journal of Crystal Growth, 2002, 237-239, 455-458.	0.7	20
167	Composition dependence of constituent phase of Feâ€“Si thin film prepared by MOCVD. Journal of Crystal Growth, 2002, 237-239, 1951-1955.	0.7	20
168	Compositional Dependence of Electrical Properties of Highly (100)-/(001)-Oriented Pb(Zr,Ti)O3Thick Films Prepared on Si Substrates by Metalorganic Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2003, 42, 5922-5926.	0.8	20
169	Preparation of Î²-Fesi2 thin film by metal organic chemical vapor deposition using iron-carbonyl and mono-silane. Thin Solid Films, 2004, 461, 40-43.	0.8	20
170	Structural modulation in bismuth cuprate superconductor observed by X-ray reciprocal space mapping. Journal of Crystal Growth, 2006, 287, 483-485.	0.7	20
171	Strain and in-plane orientation effects on the ferroelectricity of (111)-oriented tetragonal Pb(Zr0.35Ti0.65)O3 thin films prepared by metal organic chemical vapor deposition. Applied Physics Letters, 2007, 90, 222901.	1.5	20
172	Annealing Temperature Dependences of Ferroelectric and Magnetic Properties in Polycrystalline Co-Substituted BiFeO3Films. Japanese Journal of Applied Physics, 2008, 47, 7574-7578.	0.8	20
173	Experimental evidence of strain relaxed domain structure in (100)/(001)-oriented epitaxial lead titanate thick films grown by metal organic chemical vapor deposition. Journal of Applied Physics, 2008, 104, 064121.	1.1	20
174	Growth of Epitaxial KNbO₃Thick Films by Hydrothermal Method and Their Characterization. Japanese Journal of Applied Physics, 2009, 48, 09KA14.	0.8	20
175	Effect of Grain Size on Mechanical Properties of Full-Dense Pb(Zr,Ti)O₃ Ceramics. Japanese Journal of Applied Physics, 2010, 49, 09MD13.	0.8	20
176	Nanoscale Origins of Nonlinear Behavior in Ferroic Thin Films. Advanced Functional Materials, 2013, 23, 81-90.	7.8	20
177	Asymmetry in mechanical polarization switching. Applied Physics Letters, 2017, 110, .	1.5	20
178	Interface and Defect Structures of (001)-Oriented SrBi2Ta2O9 Thin Film Epitaxially Grown on (001) SrTiO3 Single Crystal. Japanese Journal of Applied Physics, 1999, 38, L1261-L1264.	0.8	19
179	Characterization of Ferroelectric Property ofC-Axis- and Non-C-Axis-Oriented Epitaxially Grown Bi2VO5.5Thin Films. Japanese Journal of Applied Physics, 2001, 40, 6481-6486.	0.8	19
180	Comparison of crystal structure and electrical properties of tetragonal and rhombohedral Pb(Zr,Ti)O3 films prepared at low temperature by pulsed-metalorganic chemical vapor deposition. Journal of Applied Physics, 2002, 92, 5448-5452.	1.1	19

#	Article	IF	Citations
181	Ferroelectricity of one-axis-preferred-oriented polycrystalline Pb(Zr,Ti)O3 films prepared by pulsed-metalorganic chemical vapor deposition. Journal of Applied Physics, 2002, 92, 6768-6772.	1.1	19
182	Characterization of Hafnium Oxide Thin Films by Source Gas Pulse Introduced Metalorganic Chemical Vapor Deposition Using Amino-Family Hf Precursors. Japanese Journal of Applied Physics, 2003, 42, 6015-6018.	0.8	19
183	Raman Spectroscopic Characterization of Tetragonal PbZrxTi1-xO3Thin Films: A Rapid Evaluation Method forc-Domain Volume. Japanese Journal of Applied Physics, 2005, 44, L827-L829.	0.8	19
184	In-situ lattice-strain analysis of a ferroelectric thin film under an applied pulse electric field. AIP Conference Proceedings, 2010, , .	0.3	19
185	In situ Raman spectroscopy for characterization of the domain contributions to electrical and piezoelectric responses in Pb(Zr,Ti)O3 films. Applied Physics Letters, 2010, 97, .	1.5	19
186	Ferroelectric and piezoelectric properties of (K,Na)NbO3 thick films prepared on metal substrates by hydrothermal method. Journal of the Korean Physical Society, 2013, 62, 1055-1059.	0.3	19
187	Interface control of a morphotropic phase boundary in epitaxial samarium modified bismuth ferrite superlattices. Physical Review B, 2014, 90, .	1.1	19
188	Large thermal hysteresis of ferroelectric transition in HfO2-based ferroelectric films. Applied Physics Letters, 2021, 118, .	1.5	19
189	Crystal structure and dielectric property of epitaxially grown (Ba, Sr)TiO₃ thin film prepared by molecular chemical vapor deposition. Journal of Materials Research, 1998, 13, 3512-3518.	1.2	18
190	Metalorganic Chemical Vapor Deposition of Epitaxial SrBi2Ta2O9 Thin Films and Their Crystal Structure. Japanese Journal of Applied Physics, 1999, 38, L258-L260.	0.8	18
191	Highly-Reproducible Preparation of Pb(Zr, Ti)O3Films at Low Deposition Temperature by Metal Organic Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2003, 42, 2801-2804.	0.8	18
192	Metalorganic chemical vapor deposition of atomically flat SrRuO3 films on stepped SrTiO3 substrates. Applied Physics Letters, 2005, 87, 052112.	1.5	18
193	Conformability of Ruthenium Dioxide Films Prepared on Substrates with Capacitor Holes by MOCVD and Modification by Annealing. Electrochemical and Solid-State Letters, 2006, 9, C175.	2.2	18
194	Cubic-on-cubic growth of a MgO(001) thin film prepared on Si(001) substrate at low ambient pressure by the sputtering method. Europhysics Letters, 2008, 81, 46001.	0.7	18
195	Electronic and Structural Properties of BiZn_{0.5}Ti_{0.5}O₃. Japanese Journal of Applied Physics, 2009, 48, 09KF05.	0.8	18
196	Orientation control of (001) and (101) in epitaxial tetragonal Pb(Zr,Ti)O3 films with (100)/(001) and (110)/(101) mixture orientations. Journal of the Ceramic Society of Japan, 2010, 118, 627-630.	0.5	18
197	Electronic, Structural, and Piezoelectric Properties of BiFe1-xCoxO3. Japanese Journal of Applied Physics, 2010, 49, 09ME07.	0.8	18
198	Structure Determination and Compositional Modification of Body-Centered Tetragonal PX-Phase Lead Titanate. Chemistry of Materials, 2011, 23, 2529-2535.	3.2	18

#	Article	IF	Citations
199	Enhancement of magnetization at morphotropic phase boundary in epitaxial BiCoO3-BiFeO3 solid solution films grown on SrTiO3 (100) substrates. Journal of Applied Physics, 2011, 109, .	1.1	18
200	Vibration-energy-harvesting properties of hydrothermally synthesized (K,Na)NbO3films deposited on flexible metal foil substrates. Japanese Journal of Applied Physics, 2015, 54, 10ND06.	0.8	18
201	Effects of starting materials on the deposition behavior of hydrothermally synthesized {1â€¯0â€¯0} -oriented epitaxial (K,Na)NbO3 thick films and their ferroelectric and piezoelectric properties. Journal of Crystal Growth, 2019, 511, 1-7.	0.7	18
202	Growth of Epitaxial SrBi2Ta2O9Thin Films by Metalorganic Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2000, 39, 2102-2109.	0.8	17
203	Crystal structure comparison between conductive SrRuO3 and CaRuO3 thin films. Journal of Crystal Growth, 2001, 229, 450-456.	0.7	17
204	Crystal Structure Analysis of Metalorganic Chemical Vapor Deposition-Î²-FeSi2Thin Film by X-ray Diffraction Measurement. Japanese Journal of Applied Physics, 2003, 42, 4943-4948.	0.8	17
205	Effect of Buffer Layer on Epitaxial Growth of YSZ Deposited on Si Substrate by Slower Q-switched 266 nm YAG Laser. Japanese Journal of Applied Physics, 2004, 43, 1532-1535.	0.8	17
206	Epitaxial Growth Map for Bi4Ti3O12Films: a Determining Factor for Crystal Orientation. Japanese Journal of Applied Physics, 2005, 44, 1337-1343.	0.8	17
207	MOCVD Growth of Bi1.5Zn1.0Nb1.5O7(BZN) Epitaxial Thin Films and Their Electrical Properties. Japanese Journal of Applied Physics, 2005, 44, 6957-6959.	0.8	17
208	Crystal structure and microstructure of epitaxial Pb(Zr,Ti)O3 films consisting of mixed phases with tetragonal and rhombohedral symmetries grown on (100)cSrRuO3//(100)SrTiO3 substrate by metalorganic chemical vapor deposition. Journal of Materials Research, 2007, 22, 1551-1557.	1.2	17
209	Raman Spectroscopy Study of Oxygen Vacancies in PbTiO₃ Thin Films Generated Heat-Treated in Hydrogen Atmosphere. Japanese Journal of Applied Physics, 2008, 47, 7510.	0.8	17
210	Raman Spectroscopy Evaluation of Oxygen Vacancy Migration by Electrical Field in Multilayer Ceramic Capacitors. Japanese Journal of Applied Physics, 2009, 48, 09KF11.	0.8	17
211	Composition control and thickness dependence of {100}-oriented epitaxial BiCoO3â€“BiFeO3 films grown by metalorganic chemical vapor deposition. Journal of Applied Physics, 2009, 105, 061620.	1.1	17
212	Characteristics of Undoped and Mn-Doped BiFeO₃Films Formed on Pt and SrRuO₃/Pt Electrodes by Radio-Frequency Sputtering. Japanese Journal of Applied Physics, 2009, 48, 09KB02.	0.8	17
213	Molecular Dynamics Simulation of 90Â° Ferroelectric Domains in PbTiO₃. Journal of the Physical Society of Japan, 2012, 81, 124702.	0.7	17
214	Influence of pulse poling on the piezoelectric property of Pb(Zr0.52,Ti0.48)O3 thin films. AIP Advances, 2014, 4, 117116.	0.6	17
215	Interface and Domain Structures of (116)-Oriented SrBi2Ta2O9 Thin Film Epitaxially Grown on (110) SrTiO3 Single Crystal. Japanese Journal of Applied Physics, 1999, 38, L1265-L1267.	0.8	16
216	A-Site-Modified Perovskite Nanosheets and Their Integration into High-Îº Dielectric Thin Films with a Clean Interface. Japanese Journal of Applied Physics, 2010, 49, 09MA01.	0.8	16

#	Article	IF	Citations
217	Crystal Structure and Dielectric Property of Bismuth Layer-Structured Dielectric Films withc-Axis Preferential Crystal Orientation. Japanese Journal of Applied Physics, 2010, 49, 09MA02.	0.8	16
218	Metal-insulator transition in V2O3 thin film caused by tip-induced strain. Applied Physics Letters, 2018, 113, .	1.5	16
219	Domain orientation relationship of orthorhombic and coexisting monoclinic phases of YO_{1.5}-doped HfO₂ epitaxial thin films. Japanese Journal of Applied Physics, 2018, 57, 11UF16.	0.8	16
220	Electric-Field-Driven Nanosecond Ferroelastic-Domain Switching Dynamics in Epitaxial <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mi>Pb</mml:mi><mml:mo stretchy="false">(</mml:mo><mml:mi>Zr</mml:mi><mml:mo>,</mml:mo><mml:mi>Ti</mml:mi><mml:mo) Tj ETQq0 0 0 rgBT /Overloc	2.9	16
221	mathvariant="normal">O</mml:mi></mml:mrow><mml:mrow><mml:mn>3</mml:mn></mml:mrow></mml:msub></mml:mrow></mml: Comparison of deposition behavior of Pb(Zr,Ti)O 3 films and its end-member-oxide films prepared by MOCVD. Thin Solid Films, 2000, 368, 261-265.	0.8	15
222	Effect of atmosphere during heating of substrate on the low temperature deposition of metalorganic chemical vapor deposited Pb(Zrx,Ti1â^'x)O3 thin films. Applied Physics Letters, 2002, 81, 898-900.	1.5	15
223	Orientation of Bi4Ti3O12-based ferroelectric thin films prepared on various kinds of substrates by metalorganic chemical vapor deposition. Journal of Crystal Growth, 2002, 235, 389-393.	0.7	15
224	Domain structures in epitaxial Pb(Zr0.68,Ti0.32)O3 thin films. Journal of Crystal Growth, 2002, 237-239, 464-467.	0.7	15
225	Preparation of hafnium oxide films from oxygen-free Hf[N(C2H5)2]4 precursor and their properties. Applied Surface Science, 2003, 216, 296-301.	3.1	15
226	Electrical Properties of (Ca,Sr)Bi4Ti4O15Thin Films Fabricated Using a Chemical Solution Deposition Method. Japanese Journal of Applied Physics, 2003, 42, 5990-5993.	0.8	15
227	Effect of Solvent on MOCVD of Pb(Zr,â€‰Ti)O[sub 3] Films with Liquid-Delivery Source Supply Method. Journal of the Electrochemical Society, 2004, 151, C463.	1.3	15
228	Enhancement of spontaneous polarization in lead zirconate titanate thin films by Dy3+ substitution. Applied Physics Letters, 2005, 87, 182906.	1.5	15
229	Satellite peaks amplified by modulation in bismuth cuprate thin film. Physica C: Superconductivity and Its Applications, 2007, 463-465, 935-938.	0.6	15
230	Solution-Based Fabrication of Perovskite Nanosheet Films and Their Dielectric Properties. Japanese Journal of Applied Physics, 2009, 48, 09KA15.	0.8	15
231	Growth of (111)-oriented BaTiO3â€“Bi(Mg0.5Ti0.5)O3 epitaxial films and their crystal structure and electrical property characterizations. Journal of Applied Physics, 2012, 111, .	1.1	15
232	Complex domain structure in relaxed PbTiO3 thick films grown on (100)cSrRuO3//(100)SrTiO3 substrates. Journal of Applied Physics, 2012, 112, .	1.1	15
233	Epitaxial ferroelectric Y-doped HfO₂ film grown by the RF magnetron sputtering. Japanese Journal of Applied Physics, 2018, 57, 11UF15.	0.8	15
234	Demonstration of ferroelectricity in ScGaN thin film using sputtering method. Applied Physics Letters, 2021, 119, .	1.5	15

#	Article	IF	Citations
235	Thermal Stability of SrRuO3Bottom Electrode and Electric Property of Pb(Zr, Ti)O3Thin Film Deposited on SrRuO3. Japanese Journal of Applied Physics, 2002, 41, 6873-6876.	0.8	14
236	Substrate effect on the crystal structure and ferroelectricity of low-temperature-deposited Pb(Zr,â€‰Ti)O3 thin films by metalorganic chemical vapor deposition. Applied Physics Letters, 2003, 82, 4122-4124.	1.5	14
237	Formation of BiFeO3â€“BiScO3Thin Films and Their Electrical Properties. Japanese Journal of Applied Physics, 2006, 45, 7321-7324.	0.8	14
238	Structural characterization by electronic transport properties on Fe₃Si films. Journal Physics D: Applied Physics, 2007, 40, 6873-6878.	1.3	14
239	Degradation-free dielectric property using bismuth layer-structured dielectrics having natural superlattice structure. Journal of the Ceramic Society of Japan, 2008, 116, 1249-1254.	0.5	14
240	Effect of bottom electrode on dielectric property of sputtered-(Ba,Sr)TiO3 films. Journal of Applied Physics, 2009, 105, 061606.	1.1	14
241	Effects of Substrate Clamping on Electrical Properties of Polycrystalline Piezoelectric Films. Japanese Journal of Applied Physics, 2009, 48, 09KD09.	0.8	14
242	Enhancement of piezoelectric response in (100)/(001) oriented tetragonal Pb(Zr, Ti)O3 films by controlling tetragonality and volume fraction of the (001) orientation. Journal of Applied Physics, 2011, 109, .	1.1	14
243	Diffraction contrast analysis of 90Â° and 180Â° ferroelectric domain structures of PbTiO₃thin films. Science and Technology of Advanced Materials, 2011, 12, 034403.	2.8	14
244	Effects of Bipolar Pulse Poling on the Ferroelectric and Piezoelectric Properties of Tetragonal Composition Pb(Zr_{0.3},Ti_{0.7})O₃ Thin Films on Microelectromechanical Systems Microcantilevers. Japanese Journal of Applied Physics, 2013, 52, 09KA01.	0.8	14
245	Ferroelectric and piezoelectric properties of KNbO₃films deposited on flexible organic substrate by hydrothermal method. Japanese Journal of Applied Physics, 2014, 53, 09PA10.	0.8	14
246	Development of a novel cell structure for low-temperature SOFC using porous stainless steel support combined with hydrogen permeable Pd layer and thin film proton conductor. Journal of Alloys and Compounds, 2016, 654, 171-175.	2.8	14
247	Charge screening strategy for domain pattern control in nano-scale ferroelectric systems. Scientific Reports, 2017, 7, 5236.	1.6	14
248	Dynamic Manipulation in Piezoresponse Force Microscopy: Creating Nonequilibrium Phases with Large Electromechanical Response. ACS Nano, 2020, 14, 10569-10577.	7.3	14
249	Preparation of near-1-Âµm-thick {100}-oriented epitaxial Y-doped HfO₂ ferroelectric films on (100)Si substrates by a radio-frequency magnetron sputtering method. Journal of the Ceramic Society of Japan, 2020, 128, 539-543.	0.5	14
250	Synthesis of New Liquid Mixed Sr-Ta and Sr-Nb Alkoxides as CVD Precursors for Metal Oxide Thin Films. Chemical Vapor Deposition, 2000, 6, 225-227.	1.4	13
251	Ferroelectric Property of a-/b-Axis-Oriented Epitaxial Sr0.8Bi2.2Ta2O9 Thin Films Grown by Metalorganic Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2002, 41, L1478-L1481.	0.8	13
252	Enhancement of Polarization Property of PZT Film by Ion-Substitution Using Rare-Earth Elements. Japanese Journal of Applied Physics, 2005, 44, 6905-6909.	0.8	13

#	Article	IF	Citations
253	Conformality of Pb(Zr,Ti)O[sub 3] Films Deposited on Trench Structures Having Submicrometer Diameter and Various Aspect Ratios. Electrochemical and Solid-State Letters, 2006, 9, C15.	2.2	13
254	In situObservation of the Fatigue-Free Piezoelectric Microcantilever by Two-Dimensional X-ray Diffraction. Japanese Journal of Applied Physics, 2009, 48, 09KA03.	0.8	13
255	Crystal Orientation Control of Bismuth Layer-Structured Dielectric Films Using Interface Layers of Perovskite-Type Oxides. Japanese Journal of Applied Physics, 2011, 50, 09NA04.	0.8	13
256	Film Thickness Dependence of Ferroelectric Properties of (111)-Oriented Epitaxial Bi(Mg_{1/2}Ti_{1/2})O₃ Films. Japanese Journal of Applied Physics, 2012, 51, 09LA04.	0.8	13
257	Growth of 130 Î¼m Thick Epitaxial KNbO3 Film by Hydrothermal Method. Materials Research Society Symposia Proceedings, 2013, 1494, 291-296.	0.1	13
258	Effects of porous flow field type separators using sintered Ni-based alloy powders on interfacial contact resistances and fuel cell performances. Energy, 2015, 87, 134-141.	4.5	13
259	Epitaxial PbZr_xTi_{1â^'x}O₃ Ferroelectric Bilayers with Giant Electromechanical Properties. Advanced Materials Interfaces, 2015, 2, 1500075.	1.9	13
260	Evaluation of oxygen vacancy in ZnO using Raman spectroscopy. , 2015, , .		13
261	Effect of thermal treatment on oxygen stoichiometry and transport properties of SrRuO3 thin films. Applied Physics Letters, 2006, 89, 242115.	1.5	12
262	Impact of (111)-Oriented SrRuO3/Pt Tailored Electrode for Highly Reproducible Preparation of Metal Organic Chemical Vapour Deposited Pb(Zr,Ti)O3Films for High Density Ferroelectric Random Access Memory Applications. Japanese Journal of Applied Physics, 2007, 46, 2139-2142.	0.8	12
263	1 V saturated Pb(Zr,Ti)O3 films with (111) orientation using lattice-matched (111)SrRuO3/(111)Pt bottom electrode prepared by pulsed metal organic chemical vapor deposition. Applied Physics Letters, 2008, 93, 152901.	1.5	12
264	In-Plane Lattice Strain Evaluation in Piezoelectric Microcantilever by Two-Dimensional X-ray Diffraction. Japanese Journal of Applied Physics, 2008, 47, 7537.	0.8	12
265	The Effect of Precursor Ligands on the Deposition Characteristics of Ru Films by MOCVD. Electrochemical and Solid-State Letters, 2009, 12, D80.	2.2	12
266	Piezoelectric Properties of {100}-Oriented Epitaxial BiCoO₃â€“BiFeO₃Films Measured Using Synchrotron X-ray Diffraction. Japanese Journal of Applied Physics, 2009, 48, 09KD06.	0.8	12
267	Effect of Film Thickness and Crystal Orientation on the Constituent Phase in Epitaxial BiFeO₃â€“BiCoO₃ Films Grown on SrTiO₃ Substrates. Japanese Journal of Applied Physics, 2010, 49, 09MB04.	0.8	12
268	Columnar grain boundary coherence in yttria-stabilized zirconia thin film: effects on ionic conductivity. Journal of the Ceramic Society of Japan, 2014, 122, 72-77.	0.5	12
269	Phase transitions associated with competing order parameters in compressively strained<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:msub><mml:mi>SrTiO</mml:mi><mml:mn>3</mml:mn></mml:msub><m films. Physical Review B, 2015, 91, .	11	12
270	Growth of Epitaxial PLZT Film by CVD. Journal of the Ceramic Society of Japan, 1991, 99, 1169-1171.	1.3	11

#	Article	IF	Citations
271	Effect of calcium modification on the microstructure and oxidation property of submicron spherical palladium powders. Journal of Materials Research, 1997, 12, 392-397.	1.2	11
272	Effect of deposition temperature on the characteristics of hafnium oxide films deposited by metalorganic chemical vapor deposition using amide precursor. Journal of Materials Research, 2004, 19, 584-589.	1.2	11
273	MOCVD of Single-Axisc-Oriented Strontium Bismuth Titanate Thin Films and Their Electrical Properties. Chemical Vapor Deposition, 2006, 12, 136-142.	1.4	11
274	Low strain sensitivity of the dielectric property of pyrochlore Biâ€“Znâ€“Nbâ€“O films. Applied Physics Letters, 2008, 92, 182901.	1.5	11
275	Epitaxially grown ferroelectric thin films for memory applications (ferroelectric random access) Tj ETQq1 1 0.784314 rgBT /Overlock 1	0.6	11
276	Domain tuning in mixed-phase BiFeO3 thin films using vicinal substrates. Applied Physics Letters, 2012, 100, 202901.	1.5	11
277	Temperature and electric field stabilities of dielectric and insulating properties for c-axis-oriented CaBi4Ti4O15 films. Journal of Applied Physics, 2013, 114, .	1.1	11
278	Orientation control of epitaxial tetragonal Pb(ZrxTi1â^'x)O3 thin films grown on (100)KTaO3 substrates by tuning the Zr/(Zrâ€‰+â€‰Ti) ratio. Applied Physics Letters, 2015, 107, .	1.5	11
279	High temperature stability of the dielectric and insulating properties of Ca(Ti, Zr)SiO5 ceramics. Applied Physics Letters, 2016, 108, .	1.5	11
280	Growth of epitaxial (K, Na)NbO3 films with various orientations by hydrothermal method and their properties. Japanese Journal of Applied Physics, 2019, 58, SLLB14.	0.8	11
281	Strain-induced resistance change in V2O3 films on piezoelectric ceramic disks. Journal of Applied Physics, 2019, 125, .	1.1	11
282	Large Electromechanical Responses Driven by Electrically Induced Dense Ferroelastic Domains: Beyond Morphotropic Phase Boundaries. ACS Applied Electronic Materials, 2020, 2, 1908-1916.	2.0	11
283	Fabrication and Evaluation of One-Axis Oriented Lead Zirconate Titanate Films Using Metalâ€“Oxide Nanosheet Interface Layer. Japanese Journal of Applied Physics, 2013, 52, 09KA04.	0.8	11
284	Enhancement of crystal anisotropy and ferroelectricity by decreasing thickness in (Al,Sc)N films. Journal of the Ceramic Society of Japan, 2022, 130, 436-441.	0.5	11
285	Deposition Condition of Epitaxially Grown PZT Films by CVD. Journal of the Ceramic Society of Japan, 1994, 102, 795-798.	1.3	10
286	Preparation of semiconductive SrTiO3 thin films by metal-organic chemical vapor deposition and their electrical properties. Journal of Materials Research, 1997, 12, 1655-1660.	1.2	10
287	Self-Organized (100)-/(001)-Preferred Orientation in Pb(Zr,Ti)O3 Films Grown on Polycrystalline Substrates by Metalorganic Chemical Vapor Deposition. Integrated Ferroelectrics, 2003, 59, 1429-1436.	0.3	10
288	Polarization comparison of Pb(Zr,Ti)O3 and Bi4Ti3O12-based ferroelectrics. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2005, 118, 23-27.	1.7	10

#	Article	IF	Citations
289	PbTiO3 content dependence of crystal structure and electrical properties of (100)-/(001)-oriented epitaxial Pb(Mg1â^•3Nb2â^•3)O3-PbTiO3 films grown by metalorganic chemical vapor deposition. Journal of Applied Physics, 2005, 98, 086112.	1.1	10
290	Twin-Free Epitaxial Films Lateral Relation between YSZ(111) and Si(111). Japanese Journal of Applied Physics, 2006, 45, L1328-L1330.	0.8	10
291	Effect of film thickness on ferroelectric domain structure and properties of Pb(Zr0.35Ti0.65)O3/SrRuO3/SrTiO3 heterostructures. Journal of Materials Science, 2009, 44, 5318-5324.	1.7	10
292	Composition dependence of crystal structure and electrical properties for epitaxial films of Bi(Zn1/2Ti1/2)O3-BiFeO3 solid solution system. Journal of the Ceramic Society of Japan, 2010, 118, 659-663.	0.5	10
293	Piezoelectric anomalies at the ferroelastic phase transitions of lead-free tungsten bronze ferroelectrics. Journal of the Ceramic Society of Japan, 2010, 118, 717-721.	0.5	10
294	Electronic and structural properties of : A proposal about the role of Ti 3s and 3p states for ferroelectricity. Solid State Communications, 2010, 150, 205-208.	0.9	10
295	Electrical properties and x-ray photoelectron spectroscopy studies of Bi(Zn0.5Ti0.5)O3 doped Pb(Zr0.4Ti0.6)O3 thin films. Journal of Applied Physics, 2010, 108, .	1.1	10
296	Nano-strip grating lines self-organized by a high speed scanning CW laser. Nanotechnology, 2011, 22, 175307.	1.3	10
297	Dielectric tunability analysis of pyrochlore Bi1.5Zn1.0Nb1.5O7 using epitaxial films on pyrochlore Bi2Ru2O7 conductive layers. Applied Physics Letters, 2014, 104, .	1.5	10
298	Large irreversible non-180Â° domain switching after poling treatment in Pb(Zr, Ti)O3 films. Applied Physics Letters, 2016, 108, .	1.5	10
299	Effect of in-plane tensile strain in (100)/(001)-oriented epitaxial PbTiO3 films on their phase transition temperature and tetragonal distortion. Applied Physics Letters, 2017, 110, .	1.5	10
300	Epitaxial growth of YO_{1.5} doped HfO₂ films on (100) YSZ substrates with various concentrations. Ferroelectrics, 2017, 512, 105-110.	0.3	10
301	Characterization of (111)-oriented epitaxial (K_{0.5}Na_{0.5})NbO₃thick films deposited by hydrothermal method. Japanese Journal of Applied Physics, 2017, 56, 10PF04.	0.8	10
302	Preparation of {001}_c-oriented epitaxial (K, Na)NbO₃ thick films by repeated hydrothermal deposition technique. Journal of the Ceramic Society of Japan, 2018, 126, 281-285.	0.5	10
303	Linear electro-optic effect in ferroelectric HfO2-based epitaxial thin films. Japanese Journal of Applied Physics, 0, , .	0.8	10
304	Thermal stability of self-polarization in a (K,Na)NbO₃ film prepared by the hydrothermal method. Japanese Journal of Applied Physics, 2021, 60, SFFB03.	0.8	10
305	Dependency of direct and inverse transverse piezoelectric properties on composition in self-polarized epitaxial (K_xNa_{1â^'x})NbO₃films grown via a hydrothermal method. Japanese Journal of Applied Physics, 2020, 59, SPPC03.	0.8	10
306	Crystal structure, ferroelectric and piezoelectric properties of epitaxial (1â^'x)(Bi_{0.5}Na_{0.5})TiO₃â€“x(Bi_{0.5}K_{0.5})TiO₃ films grown by hydrothermal method. Japanese Journal of Applied Physics, 2020, 59, SPPB10.	0.8	10

#	Article	IF	Citations
307	Growth of Epitaxial 100-Oriented KNbO3â€“NaNbO3Solid Solution Films on (100)cSrRuO3â^¥(100)SrTiO3by Hydrothermal Method and Their Characterization. Japanese Journal of Applied Physics, 2011, 50, 09ND11.	0.8	10
308	Thickness dependence of phase stability in epitaxial <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mrow><mml:mo>(</mml:mo><mml:msub><mml:mi>Hf</mml:mi><mml:mi mathvariant="normal">O</mml:mi><mml:mn>2</mml:mn></mml:msub></mml:mrow></mml:math> films. Physical Review Materials, 2021, 5, .	0.9	10
309	Characterization of Epitaxially Grown CVD-Pb(Zr, Ti) O₃ Films with High Deposition Rate. Journal of the Ceramic Society of Japan, 1994, 102, 114-118.	1.3	9
310	Evolution of Particle Structure during the Formation of Single-Crystal Spherical Palladium Particles by Spray Pyrolysis. Journal of the Ceramic Society of Japan, 1997, 105, 299-303.	1.3	9
311	Preparation of SrRuO₃ and CaRuO₃ Films by Mocvd and its Application to Electrodes for Ferroelectric Thin Films. Materials Research Society Symposia Proceedings, 1999, 596, 79.	0.1	9
312	New preparation process of Pb(Zr_xTi_{1â^'x})O₃ thin films from PbZrO₃ and PbTiO₃ multilayers. Journal of Materials Research, 2002, 17, 2217-2226.	1.2	9
313	Ferroelectric Properties of Dysprosium-Substituted Lead Zirconate Titanate Thin Films Fabricated by Chemical Solution Deposition. Japanese Journal of Applied Physics, 2004, 43, 6558-6561.	0.8	9
314	â€œLOCAL EPITAXIAL GROWTHâ€•OF TETRAGONAL (111)-ORIENTED Pb(Zr,Ti)O3 THIN FILM. Integrated Ferroelectrics, 2005, 75, 3-9.	0.3	9
315	Site Occupancy Analysis on the Enhancement in Dy-Substituted Pb(Zr,Ti)O3Film. Japanese Journal of Applied Physics, 2006, 45, 7548-7551.	0.8	9
316	Solution-Based Fabrication of High-Îº Dielectric Nanofilms Using Titania Nanosheets as a Building Block. Japanese Journal of Applied Physics, 2007, 46, 6979.	0.8	9
317	Î²-FeSi2 growth on Cu-mediated Si substrate and enhancement of photoluminescence. Thin Solid Films, 2007, 515, 8144-8148.	0.8	9
318	Morphology of solâ€“gel produced composite films for optical oxygen sensors. Applied Surface Science, 2008, 254, 1545-1558.	3.1	9
319	Impact of 90Â°-Domain Wall Motion in Pb(Zr_{0.43}Ti_{0.57})O₃Film on the Ferroelectricity Induced by an Applied Electric Field. Applied Physics Express, 0, 2, 041401.	1.1	9
320	Preparation of (001)-Oriented CaBi4Ti4O15and SrBi4Ti4O15Films Using LaNiO3Nucleation Layer on Pt-passivated Si Wafer. Japanese Journal of Applied Physics, 2009, 48, 09KA10.	0.8	9
321	Deposition of undoped indium oxide thin films on stripe-patterned substrates by spray CVD. Journal of Crystal Growth, 2009, 311, 642-646.	0.7	9
322	Combinatorial preparation process of Pb(Zr1-xTix)O3 thin films by chemical solution deposition method. Journal of the Ceramic Society of Japan, 2009, 117, 698-702.	0.5	9
323	Effect of Deposition Time on Film Thickness and Their Properties for Hydrothermally-Grown Epitaxial KNbO₃ Thick Films. Japanese Journal of Applied Physics, 2010, 49, 07HF01.	0.8	9
324	Preparation and Characteristics of Bi_{0.5}Na_{0.5}TiO₃ Singleâ€Crystalline Films by a Solidâ€State Process. Journal of the American Ceramic Society, 2011, 94, 3291-3295.	1.9	9

#	Article	IF	Citations
325	Ba(Zr Ti1â^')O3 thin films for tunable microwave applications. Ceramics International, 2015, 41, S323-S330.	2.3	9
326	Preparation of preferentially (111)-oriented Mg₂Si thin films on (001)Al₂O₃ and (100)CaF₂ substrates and their thermoelectric properties. Japanese Journal of Applied Physics, 2017, 56, 05DC02.	0.8	9
327	Preparation of 1ÂÎ¼m thick Y-doped HfO₂ ferroelectric films on (111)Pt/TiO _x /SiO₂/(001)Si substrates by a sputtering method and their ferroelectric and piezoelectric properties. Japanese Journal of Applied Physics, 2021, 60, 031009.	0.8	9
328	High yield preparation of (100)_c-oriented (K,Na)NbO₃ thick films by hydrothermal method using amorphous niobium source. Journal of the Ceramic Society of Japan, 2020, 128, 512-517.	0.5	9
329	Deposition characteristics and properties of iron nitride films by CVD using organometallic compound. Journal of Materials Science, 1990, 25, 5303-5312.	1.7	8
330	Preparation of Semiconductive Epitaxial BaTiO₃ Thin Film and its Electrical Properties. Journal of the Ceramic Society of Japan, 1996, 104, 75-77.	1.3	8
331	Characterization of Ferroelectric Property of c-axis and non-c-axis Oriented Epitaxially Grown Bismuth Layer-Structured Ferroelectric Thin Films with Different m-numbers Prepared by MOCVD. Materials Research Society Symposia Proceedings, 2000, 655, 234.	0.1	8
332	Residual strain analysis of epitaxial grown SBT thin films prepared by MOCVD. Integrated Ferroelectrics, 2001, 33, 59-69.	0.3	8
333	Characterization of Epitaxial Pb(Zr_x,Ti_{1-x})O₃ Thin Films with Composition Near the Morphotropic Phase Boundary. Materials Research Society Symposia Proceedings, 2002, 748, 1.	0.1	8
334	Quantitative Effects of Preferred Orientation and Impurity Phases on Ferroelectric Properties of SrBi2(Ta1-xNbx)2O9Thin Films Measured by X-Ray Diffraction Reciprocal Space Mapping. Japanese Journal of Applied Physics, 2003, 42, 539-543.	0.8	8
335	Photoluminescence properties of Si/Î²-FeSi2/Si double heterostructure. Thin Solid Films, 2006, 508, 380-384.	0.8	8
336	Growth Behavior ofc-Axis-Oriented Epitaxial SrBi2Ta2O9Films on SrTiO3Substrates with Atomic Scale Step Structure. Japanese Journal of Applied Physics, 2006, 45, L138-L141.	0.8	8
337	Strain-relaxed structure in (001)/(100)-oriented epitaxial Pb(Zr,Ti)O3 films grown on (100) SrTiO3 substrates by metal organic chemical vapor deposition. Journal of Applied Physics, 2009, 105, .	1.1	8
338	Single crystal-like selection rules for unipolar-axis oriented tetragonal Pb(Zr,Ti)O3 thick epitaxial films. Applied Physics Letters, 2010, 97, 111901.	1.5	8
339	Growth of Orientation-Controlled Epitaxial KNbO₃ Thin Film by Hydrothermal Method. Key Engineering Materials, 0, 485, 199-202.	0.4	8
340	Unusual 90Â° domain structure in (2/3)Bi(Zn1/2Ti1/2)O3-(1/3)BiFeO3 epitaxial films with giant 22% tetragonal distortion. Applied Physics Letters, 2013, 103, .	1.5	8
341	Epitaxial growth of Mg₂Si films on strontium titanate single crystals. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 1688-1691.	0.8	8
342	Photovoltaic properties of Si-based quantum-dot-sensitized solar cells prepared using laser plasma in liquid. Japanese Journal of Applied Physics, 2014, 53, 010208.	0.8	8

#	Article	IF	Citations
343	Domain structure of tetragonal Pb(Zr,Ti)O₃ nanorods and its size dependence. Japanese Journal of Applied Physics, 2015, 54, 10NA07.	0.8	8
344	Fabrication and characterization of (110)-oriented (Ba0.5,Sr0.5)TiO3thin films using PdO//Pd buffer layer. Japanese Journal of Applied Physics, 2015, 54, 10NA15.	0.8	8
345	Thermally stable dielectric responses in uniaxially (001)-oriented CaBi4Ti4O15 nanofilms grown on a Ca2Nb3O10â˜’ nanosheet seed layer. Scientific Reports, 2016, 6, 20713.	1.6	8
346	Growth of epitaxial tetragonal (Bi,K)TiO3films and their ferroelectric and piezoelectric properties. Japanese Journal of Applied Physics, 2016, 55, 10TA13.	0.8	8
347	Enhancement of Dielectric Properties in Epitaxial Bismuth Ferriteâ€“Bismuth Samarium Ferrite Superlattices. Advanced Electronic Materials, 2016, 2, 1600170.	2.6	8
348	Growth of (111)-oriented epitaxial magnesium silicide (Mg2Si) films on (001) Al2O3 substrates by RF magnetron sputtering and their properties. Journal of Materials Science, 2018, 53, 5151-5158.	1.7	8
349	Formation of polar phase in Fe-doped ZrO2 epitaxial thin films. Applied Physics Letters, 2018, 113, .	1.5	8
350	Domain structure transition from two to three dimensions in tensile strained (100)/(001)-oriented epitaxial tetragonal PZT film. Applied Physics Letters, 2018, 113, .	1.5	8
351	Stability of the orthorhombic phase in (111)-oriented YO_{1.5}-substituted HfO₂ films. Journal of the Ceramic Society of Japan, 2018, 126, 269-275.	0.5	8
352	Effect of Ta-substitution on the deposition of (K,Na)(Nb,Ta)O3 films by hydrothermal method. Japanese Journal of Applied Physics, 2019, 58, SLLB12.	0.8	8
353	Good piezoelectricity of self-polarized thick epitaxial (K,Na)NbO3 films grown below the Curie temperature (240â€‰Â°C) using a hydrothermal method. Applied Physics Letters, 2020, 117, .	1.5	8
354	Bayesian inference in band excitation scanning probe microscopy for optimal dynamic model selection in imaging. Journal of Applied Physics, 2020, 128, 054105.	1.1	8
355	Structural and electrical characterization of hydrothermally deposited piezoelectric (K,Na)(Nb,Ta)O3 thick films. Journal of Materials Science, 2020, 55, 8829-8842.	1.7	8
356	Temperature dependence on the domain structure of epitaxial PbTiO₃ films grown on single crystal substrates with different lattice parameters. Japanese Journal of Applied Physics, 2020, 59, SPPB01.	0.8	8
357	Low-temperature deposition of Li substituted (K,Na)NbO₃ films by a hydrothermal method and their structural and ferroelectric properties. Journal of the Ceramic Society of Japan, 2019, 127, 388-393.	0.5	8
358	Large Piezoelectric Response in Lead-Free (Bi_{0.5}Na_{0.5})TiO₃-Based Perovskite Thin Films by Ferroelastic Domain Switching: Beyond the Morphotropic Phase Boundary Paradigm. ACS Applied Materials & Interfaces, 2021, 13, 57532-57539.	4.0	8
359	Deposition conditions of SrTiO3 films on various substrates by CVD and their dielectric properties. Thin Solid Films, 1998, 334, 71-76.	0.8	7
360	CVD of SrBi₂Ta₂O₉(SBT) Thin Film from Bi(CH₃)₃ - Sr[Ta(OÂ·C₂H₅)₆]₂ - O₂ System. Key Engineering Materials, 1999, 169-170, 145-148.	0.4	7

#	Article	IF	Citations
361	Good Ferroelectricity of Pb(Zr,Ti)O3Thin Films Fabricated by Highly Reproducible Deposition on Bottom Ir Electrode at 395Â°C. Japanese Journal of Applied Physics, 2003, 42, L1083-L1086.	0.8	7
362	Selective reaction and chemical anisotropy in epitaxial bismuth layer-structured ferroelectric thin films. Journal of Solid State Chemistry, 2005, 178, 64-71.	1.4	7
363	Comparison of electrical properties of (100)âˆ•(001)-oriented epitaxial Pb(Zr0.35,Ti0.65)O3 thin films with the same (001) domain fraction grown on (100)Si and (100)SrTiO3 substrates. Applied Physics Letters, 2005, 87, 182907.	1.5	7
364	Effect of template layer on formation of flat-surface Î²-FeSi2 epitaxial films on (111) Si by metal-organic chemical vapor deposition. Journal of Crystal Growth, 2006, 289, 37-43.	0.7	7
365	Good Conformability of Indium-Tin Oxide Thin Films Prepared by Spray Chemical Vapor Deposition. Electrochemical and Solid-State Letters, 2009, 12, D42.	2.2	7
366	Novel Highly Volatile MOCVD Precursors for Ta2O5 and Nb2O5 Thin Films. ECS Transactions, 2009, 16, 243-251.	0.3	7
367	MOCVD growth and characterization of BiFeO3â€“Bi(Zn1/2Ti1/2)O3 ferroelectric films. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2010, 173, 14-17.	1.7	7
368	Influence of Epitaxial Growth Orientation on Residual Strain and Dielectric Properties of (Ba_{0.3}Sr_{0.7})TiO₃Films Grown on In-Plane Compressive Substrates. Ferroelectrics, 2010, 405, 262-267.	0.3	7
369	Growth of (111)-Oriented Epitaxial Bi(Mg_{0.5}Ti_{0.5})O₃ Films and their Characterization. Key Engineering Materials, 2011, 485, 195-198.	0.4	7
370	Oxygen vacancies in PbTiO₃ thin films probed by resonant Raman spectroscopy. Journal of the Ceramic Society of Japan, 2013, 121, 598-601.	0.5	7
371	Effects of heat treatment on electrical and electromechanical properties of hydrothermally synthesized epitaxial (K_{0.51}Na_{0.49})NbO₃ films. Japanese Journal of Applied Physics, 2014, 53, 05FE02.	0.8	7
372	Effect of incubation time on preparation of continuous and flat Ru films. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2015, 33, .	0.9	7
373	Crystal structure and compositional analysis of epitaxial (K_{0.56}Na_{0.44})NbO₃films prepared by hydrothermal method. Journal of Materials Research, 2016, 31, 693-701.	1.2	7
374	Direct Imaging of the Relaxation of Individual Ferroelectric Interfaces in a Tensileâ€Strained Film. Advanced Electronic Materials, 2017, 3, 1600508.	2.6	7
375	Deposition of orientation-controlled thick (K,Na)NbO₃ films on metal substrates by repeated hydrothermal deposition technique. Journal of the Ceramic Society of Japan, 2019, 127, 478-484.	0.5	7
376	Influence of orientation on the electro-optic effect in epitaxial Y-doped HfO₂ ferroelectric thin films. Japanese Journal of Applied Physics, 2021, 60, SFFB13.	0.8	7
377	Rapid deposition of (K,Na)NbO3 thick films using microwave-assisted hydrothermal technique. Japanese Journal of Applied Physics, 2020, 59, SPPB02.	0.8	7
378	Ferroelectric and piezoelectric properties of 100â€‰nm-thick CeO2-HfO2 epitaxial films. Applied Physics Letters, 2022, 120, .	1.5	7

#	Article	IF	Citations
379	Preparation of PZT Film on (100)Pt/(100) MgO Substrate by CVD and Its Properties. Journal of the Ceramic Society of Japan, 1994, 102, 128-132.	1.3	6
380	Formability and Sinterability of Hydrothermally Crystallized Monodispersed Titanium Dioxide Particles. Journal of the Ceramic Society of Japan, 1995, 103, 552-556.	1.3	6
381	General rule for the determination of c-axis orientation of Pb-based tetragonal ferroelectric oxide film prepared by CVD. Journal of Materials Science Letters, 1995, 14, 629-632.	0.5	6
382	Effect of KrF excimer laser irradiation on low-temperature preparation of lead titanium oxide film by metalorganic chemical vapor deposition. Materials Research Bulletin, 1995, 30, 1081-1088.	2.7	6
383	Modification of semiconductive BaTiO3 film and its electrical properties. Materials Research Bulletin, 1996, 31, 1233-1241.	2.7	6
384	Comparison Study of (001)-/(100)-Oriented Epitaxial and Fiber-Textured Pb(Zr,Ti)O3Thick Films Prepared by MOCVD. Integrated Ferroelectrics, 2004, 64, 217-225.	0.3	6
385	Field-induced strain of (Pb, La)(Zr, Ti)O3 epitaxial films grown by metal organic chemical vapor deposition. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2005, 120, 161-165.	1.7	6
386	Electrooptic and Piezoelectric Properties of (Pb,La)(Zr,Ti)O3Films with Various Zr/Ti Ratios. Japanese Journal of Applied Physics, 2008, 47, 7541-7544.	0.8	6
387	X-ray diffraction study of polycrystalline BiFeO3 thin films under electric field. Applied Physics Letters, 2008, 93, 042907.	1.5	6
388	Composition Dependency of Epitaxial Pb(Zr,Ti)O₃Films with Different Film Thickness. Ferroelectrics, 2009, 389, 10-17.	0.3	6
389	Antiferrodistortive Structural Phase Transition in Compressively-Strained Epitaxial SrTiO3 Film Grown on (La, Sr)(Al, Ta)O3 Substrate. Integrated Ferroelectrics, 2010, 115, 57-62.	0.3	6
390	Buffer-layer-enhanced growth of a single-domain LaB6 (100) epitaxial thin film on a MgO (100) substrate via pulsed laser deposition. Journal of Crystal Growth, 2011, 330, 39-42.	0.7	6
391	Film Thickness Dependence of Crystal Structure in 100-Oriented Epitaxial Pb(Zr_{0.65}Ti_{0.35})O₃ Films Grown on Single-Crystal Substrates with Different Thermal Expansion Coefficients. Japanese Journal of Applied Physics, 2012, 51, 09LA14.	0.8	6
392	Phase Boundary Shift by Thermal Strain in 100-Oriented Epitaxial Pb(ZrxTi1-x)O3Film Grown on CaF2Substrates. Japanese Journal of Applied Physics, 2013, 52, 09KA02.	0.8	6
393	High Temperature Reproducible Preparation of Mg2Si Films on (001)Al2O3 substrates Using RF Magnetron Sputtering Method. Materials Research Society Symposia Proceedings, 2014, 1642, 1.	0.1	6
394	Polar-axis-oriented crystal growth of tetragonal PZT films on stainless steel substrate using pseudo-perovskite nanosheet buffer layer. AIP Advances, 2015, 5, .	0.6	6
395	Fabrication of highly (110)-oriented BaCeO₃-based proton-conductive oxide thin films by RF magnetron sputtering method. Japanese Journal of Applied Physics, 2016, 55, 02BC19.	0.8	6
396	Preparation of Ca-Si Films on (001) Al2O3 Substrates by an RF Magnetron Sputtering Method and Their Electrical Properties. Journal of Electronic Materials, 2016, 45, 3121-3126.	1.0	6

#	Article	IF	Citations
397	Growth of {110}-one-axis-oriented perovskite-type oxide films using self-aligned epitaxial (101)PdO//(111) Pd double layers. Thin Solid Films, 2016, 599, 133-137.	0.8	6
398	Experimental study of effect of strain on electrocaloric effect in (001)-epitaxial (Ba,Sr)TiO₃ thin films. Japanese Journal of Applied Physics, 2017, 56, 10PF15.	0.8	6
399	Evaluation of phase and thermoelectric properties of thin film SrSi₂. Journal of the Ceramic Society of Japan, 2019, 127, 394-398.	0.5	6
400	Superdomain structure and high conductivity at the vertices in the (111)-oriented epitaxial tetragonal Pb(Zr,Ti)O3 thin film. Current Applied Physics, 2019, 19, 418-423.	1.1	6
401	Impact of Deposition Temperature on Crystal Structure and Ferroelectric Properties of (Al_{1â^'x}Sc_x)N Films Prepared by Sputtering Method. Physica Status Solidi (A) Applications and Materials Science, 2021, 218, 2100302.	0.8	6
402	Influence of cooling rate on ferroelastic domain structure for epitaxial (100)/(001)-oriented Pb(Zr,) Tj ETQq0 0 0 rgBT /Overlock 10 Tf 50	0.8	6
403	Crystal Orientation Control of Bismuth Layer-Structured Dielectric Films Using Interface Layers of Perovskite-Type Oxides. Japanese Journal of Applied Physics, 2011, 50, 09NA04.	0.8	6
404	Preparation and Characterization of Ba(Zr_xTi_{1-x})O₃Thin Films Using Reactive Sputtering Method. Japanese Journal of Applied Physics, 2012, 51, 09LA01.	0.8	6
405	Film Thickness Dependence of Ferroelectric Properties of (111)-Oriented Epitaxial Bi(Mg1/2Ti1/2)O3Films. Japanese Journal of Applied Physics, 2012, 51, 09LA04.	0.8	6
406	Polar-axis-oriented epitaxial tetragonal (Bi,K)TiO3 films with large remanent polarization deposited below Curie temperature by a hydrothermal method. Applied Physics Letters, 2022, 120, 022903.	1.5	6
407	Preparation of iron nitride films from organometallic compound. Journal of Materials Science Letters, 1988, 7, 851-852.	0.5	5
408	Thermal Stability of Pb(C11H19O2)2 Used as the Lead Source in MOCVD. Chemical Vapor Deposition, 2000, 6, 311-314.	1.4	5
409	Electrical Properties of Polycrystalline and Epitaxially Grown PZT Thin Films. Key Engineering Materials, 2002, 216, 83-86.	0.4	5
410	Source Gas Pulse-Introduced MOCVD of HfO[sub 2] Thin Films using Hf(O-t-C[sub 4]H[sub 9])[sub 4]. Journal of the Electrochemical Society, 2004, 151, C698.	1.3	5
411	Perovskite Single-Phase Growth of Epitaxial Pb(Zn1/3Nb2/3)O3Films by Alternative-Source-Gas-Introduced Metalorganic Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2005, 44, L1452-L1455.	0.8	5
412	Epitaxial Growth of (100)-Oriented Î²-FeSi2Thin Films on Insulating Substrates. Japanese Journal of Applied Physics, 2005, 44, 2496-2501.	0.8	5
413	In situ FTIR investigation of the effect of gas-phase reaction on the deposition of Pb(Zr,Ti)O3 films by MOCVD. Thin Solid Films, 2006, 498, 277-281.	0.8	5
414	Domain structures in highly (100)-oriented epitaxial Pb(Zr0.35,Ti0.65)O3 thin films. Journal of Applied Physics, 2007, 101, 064112.	1.1	5

#	Article	IF	Citations
415	Enhancement of field-induced strain by La substitution in epitaxial Pb(Zr,Ti)O3 films grown by metal organic chemical vapor deposition. Applied Physics Letters, 2007, 90, 262902.	1.5	5
416	(111)-oriented Pb(Zr,Ti)O3 films deposited on SrRuO3âˆ•Pt electrodes: Reproducible preparation by metal organic chemical vapor deposition, top electrode influence, and reliability. Journal of Applied Physics, 2007, 102, 114105.	1.1	5
417	Epitaxial Growth of Ferromagnetic Iron Silicide Thin Films on Silicon with Yttria-Stabilized Zirconia Buffer Layer. Japanese Journal of Applied Physics, 2008, 47, 577-579.	0.8	5
418	Synchrotron X-ray diffraction study on a single nanowire of PX-phase lead titanate. Journal of the European Ceramic Society, 2010, 30, 3259-3262.	2.8	5
419	Preferential Crystal Growth of (100)-Oriented BiFeO3Films on Si Substrate. IOP Conference Series: Materials Science and Engineering, 2011, 18, 092033.	0.3	5
420	Thickness-dependent ferroelectric properties of Mn-doped BiFeO3 films formed on Pt and SrRuO3/Pt electrodes by RF Sputtering. Current Applied Physics, 2011, 11, S228-S231.	1.1	5
421	Application of synchrotron-based reciprocal-space mapping at a fixed angular position to identification of crystal symmetry of Bi₄Ti₃O₁₂epitaxial thin films. Journal of Applied Crystallography, 2011, 44, 385-391.	1.9	5
422	Linear actuation piezoelectric microcantilever using tetragonal composition PZT thin films. , 2013, , .		5
423	Small-strain (100)/(001)-oriented epitaxial PbTiO₃ films with film thickness ranging from nano- to micrometer order grown on (100)CaF₂ substrates by metal organic chemical vapor deposition. Journal of Materials Research, 2013, 28, 696-701.	1.2	5
424	Investigation of PbTiO₃ thin films with reduced and re-oxidized treatment using Raman spectroscopy. Journal of the Ceramic Society of Japan, 2013, 121, 859-862.	0.5	5
425	Influence of Ba/Sr ratio in compressively-strained (Ba,Sr)TiO₃(001) films on the ferroelectric phase transition. Journal of the Ceramic Society of Japan, 2013, 121, 690-692.	0.5	5
426	Preparation and characterization of Ba(ZrxTi1âˆ’x)O3thin films for high-frequency applications. Japanese Journal of Applied Physics, 2014, 53, 09PB04.	0.8	5
427	Fabrication of (100)_c-oriented Mn-doped bismuth ferrite films on silicon and stainless steel substrates using calcium niobate nanosheets. Journal of the Ceramic Society of Japan, 2015, 123, 322-328.	0.5	5
428	Photoluminescent iron disilicide on modified Si surface by using silver. Japanese Journal of Applied Physics, 2015, 54, 07JB04.	0.8	5
429	Orientation control of barium titanate films using metal oxide nanosheet layer. Japanese Journal of Applied Physics, 2016, 55, 10TA15.	0.8	5
430	Control of p- and n-type Conduction in Thermoelectric Non-doped Mg2Si Thin Films Prepared by Sputtering Method. MRS Advances, 2018, 3, 1355-1359.	0.5	5
431	Ferroelectric properties of epitaxial Bi₂SiO₅ thin films grown on SrTiO₃ substrates with various orientations. Japanese Journal of Applied Physics, 2019, 58, SLLB04.	0.8	5
432	Lower ferroelectric coercive field of ScGaN with equivalent remanent polarization as ScAlN. Applied Physics Express, 2022, 15, 081003.	1.1	5

#	Article	IF	Citations
433	Preparation of TaN_x-TiN Films by CVD. Journal of the Ceramic Society of Japan, 1990, 98, 168-173.	1.3	4
434	The Effect of Ti/Sr Ratio on Grain Growth of La-Doped SrTiO₃ Ceramics. Journal of the Ceramic Society of Japan, 1996, 104, 190-195.	1.3	4
435	Characteristics of Pb(Zr, Ti)O3thin films prepared on various substrates by source gas pulse-introduced metalorganic chemical vapor deposition. Ferroelectrics, 2001, 260, 69-74.	0.3	4
436	Low Temperature Preparation of High-Quality Pb(Zr,Ti)O₃ Films by Metal Organic Chemical Vapor Deposition with High Reproducibility. Materials Research Society Symposia Proceedings, 2001, 688, 1.	0.1	4
437	A Novel Ruthenium Precursor for MOCVD without Seed Ruthenium Layer. Materials Research Society Symposia Proceedings, 2002, 748, 1.	0.1	4
438	Novel Candidate of c-axis-oriented BLSF Thin Films for High-Capacitance Condenser. Materials Research Society Symposia Proceedings, 2002, 748, 1.	0.1	4
439	Preparation of SrBi 2 Ta 2 O 9 Thin Films by Liquid-Delivery MOCVD Without Additional Solvents. Integrated Ferroelectrics, 2002, 45, 215-222.	0.3	4
440	Sample Geometry Effects on Electric-Field-Induced Displacements in Piezoelectric Thin Films Measured by Atomic Force Microscopy. Materials Research Society Symposia Proceedings, 2003, 784, 11291.	0.1	4
441	Growth of Pyrochlore Bi2Ti2O7 Epitaxial Films and Their Electrical Characterization. Integrated Ferroelectrics, 2004, 67, 201-209.	0.3	4
442	Effect of Deposition Temperature and Post-Heat-Treatment Condition on the Characteristics of (100)-Self-Orientation LaNiO₃ Films Prepared by RF Magnetron Sputter Deposition. Materials Research Society Symposia Proceedings, 2004, 833, 57.	0.1	4
443	Structural and Electrical Properties of Polycrystalline Bi4-xNdxTi3O12Ferroelectric Thin Films with in-Planec-Axis Orientations. Japanese Journal of Applied Physics, 2005, 44, L292-L294.	0.8	4
444	CRYSTAL ORIENTATION ANISOTROPY OF EPITAXIAL Pb(Mg1/3Nb2/3)O3-PbTiO3 THICK FILMS GROWN BY MOCVD. Integrated Ferroelectrics, 2006, 80, 67-76.	0.3	4
445	Structural Property and Electric Field Response of a Single Perovskite PbTiO3Nanowire Using Micro X-ray Beam. Japanese Journal of Applied Physics, 2010, 49, 09MC09.	0.8	4
446	EVALUATION OF RELATIVE VOLUME FRACTION OF TETRAGONAL PHASE AND RHOMBOHEDRAL PHASE IN Pb(Zr,Ti)O₃ FILM BY RAMAN SPECTROSCOPY. Integrated Ferroelectrics, 2010, 112, 33-41.	0.3	4
447	Comparison of BST film microwave tunable devices based on (100) and (111) MgO substrates. IEEE Transactions on Ultrasonics, Ferroelectrics, and Frequency Control, 2010, 57, 2221-2227.	1.7	4
448	High Fatigue Endurance and Large Remanent Polarization in Pt/SrRuO$_{3}$/BiFe$_{0.95}$Mn$_{0.05}$O$_{3}$/SrRuO$_{3}$/Pt Ferroelectric Capacitors Formed on SiO$_{2}$-Coated Si Substrates. Applied Physics Express, 2011, 4, 081501.	1.1	4
449	Growth of (111) One-Axis-Oriented Bi(Mg1/2Ti1/2)O3Films on (100)Si Substrates. Japanese Journal of Applied Physics, 2013, 52, 04CH09.	0.8	4
450	Evaluation of Î²-FeSi2/Si-interface using Ag-coating on Si surface. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 1684-1687.	0.8	4

#	Article	IF	Citations
451	Structural and dielectric properties of BaTiO3â€“Bi(Mg1/2Ti1/2)O3thin films fabricated by chemical solution deposition. Japanese Journal of Applied Physics, 2014, 53, 09PA11.	0.8	4
452	Lead- and alkali-metal-free BaTiO3â€“Bi(Mg0.5Ti0.5)O3â€“BiFeO3solid-solution thin films with high dielectric constant prepared on Si substrates by solution-based method. Japanese Journal of Applied Physics, 2014, 53, 09PA12.	0.8	4
453	Control of Iron Disilicide Crystal Structure by Using Liquid Phase Obtained by Au-Si Eutectic Reaction. Materials Research Society Symposia Proceedings, 2015, 1760, 139.	0.1	4
454	Pulse poling within 1 second enhance the piezoelectric property of PZT thin films. , 2015, , .		4
455	Simultaneous achievement of high dielectric constant and low temperature dependence of capacitance in (111)-oriented BaTiO3-Bi(Mg0.5Ti0.5)O3-BiFeO3 solid solution thin films. AIP Advances, 2016, 6, .	0.6	4
456	Angular dependence of Raman spectrum for Pb(Zr,Ti)O3epitaxial films. Japanese Journal of Applied Physics, 2016, 55, 10TC07.	0.8	4
457	Metalâ€“organic chemical vapor deposition growth of Î²-FeSi₂/Si composite powder via vaporâ€“liquidâ€“solid method and its photocatalytic properties. Japanese Journal of Applied Physics, 2016, 55, 06HC02.	0.8	4
458	Dynamic observation of ferroelectric domain switching using scanning nonlinear dielectric microscopy. Japanese Journal of Applied Physics, 2017, 56, 10PF16.	0.8	4
459	In-plane orientation and composition dependences of crystal structure and electrical properties of {100}-oriented Pb(Zr,Ti)O₃films grown on (100) Si substrates by metal organic chemical vapor deposition. Japanese Journal of Applied Physics, 2017, 56, 10PF12.	0.8	4
460	Indirect measurements of electrocaloric effect in ferroelectric thin films by positive-up-negative-down method. Journal of the Ceramic Society of Japan, 2017, 125, 441-444.	0.5	4
461	MOCVD growth of Î²-FeSi2 film on modified Si surface by silver and enhancement of luminescence. Journal of Crystal Growth, 2019, 506, 131-134.	0.7	4
462	Epitaxial growth of Mg₂Si films on (111) Si substrates covered with epitaxial SiC layers. Japanese Journal of Applied Physics, 2020, 59, SF1001.	0.8	4
463	Barkhausen noise analysis of thin film ferroelectrics. Applied Physics Letters, 2020, 117, 012902.	1.5	4
464	Thermoelectric (Ba x Sr1â€“x)Si2 films prepared by sputtering method over the barium solubility limit. Japanese Journal of Applied Physics, 2020, 59, SFFB02.	0.8	4
465	Capacitor Applications of c-Axis-Oriented Bismuth Layer Structured Ferroelectric Thin Films. Ceramic Engineering and Science Proceedings, 0, , 57-64.	0.1	4
466	Local Câ€“V mapping for ferroelectrics using scanning nonlinear dielectric microscopy. Journal of Applied Physics, 2020, 128, 244105.	1.1	4
467	X-ray Diffraction Study of Electric-field-induced Strains in Polycrystalline BiFeO3 Thin Films at Low Temperature Using Synchrotron Radiation. Journal of the Korean Physical Society, 2011, 59, 2556-2559.	0.3	4
468	Optimization of deposition conditions of yttrium doped-SrZrO₃ thin films fabricated by pulsed laser deposition. Journal of the Ceramic Society of Japan, 2020, 128, 436-440.	0.5	4

#	Article	IF	Citations
469	Preparation of Niobium Nitride Films by CVD. Journal of the Ceramic Association Japan, 1987, 95, 65-68.	0.2	3
470	Residual Strain in Epitaxially-grown PbTiO3 and PZT Films Prepared on (100)MgO Substrates by MOCVD.. Nippon Kagaku Kaishi / Chemical Society of Japan - Chemistry and Industrial Chemistry Journal, 1995, 1995, 789-795.	0.1	3
471	Preparation of Al-doped PbTiO3Thin Films by Metalorganic Chemical Vapor Deposition and Their Characterization. Japanese Journal of Applied Physics, 2000, 39, 3591-3595.	0.8	3
472	Preparation of SrBi2(Ta0.7Nb0.3)2O9â€“Bi3TaTiO9 solid solution films by MOCVD and their properties. Journal of Crystal Growth, 2002, 237-239, 473-477.	0.7	3
473	Synthesis and Properties of Nd-Substituted Bismuth Titanate Polycrystalline Thin Films with Polar-Axis Orientation. Key Engineering Materials, 2004, 269, 53-56.	0.4	3
474	Comparison of the Ferroelectricity for 70â€“80 nm Thick Pb(Zr,Ti)O3 Films Deposited on (111)Ir Bottom Electrodes at Different Temperatures by MOCVD. Integrated Ferroelectrics, 2004, 68, 147-154.	0.3	3
475	Effect of oxygen pressure on structural modulation observed by X-ray reciprocal space mapping in epitaxial bismuth cuprate superconducting film. Europhysics Letters, 2005, 71, 686-691.	0.7	3
476	Structural Modulation in Oxygen Deficient Epitaxial Bi2Sr2Ca1Cu2OXObserved by X-ray Reciprocal Space Mapping. Japanese Journal of Applied Physics, 2005, 44, 156-157.	0.8	3
477	Electric-Field-Induced Displacements in Pt/PZT/Pt/SiO2/Si System Investigated by Finite Element Method: Material-Constant Dependences. Materials Research Society Symposia Proceedings, 2005, 902, 1.	0.1	3
478	INVESTIGATION OF Sr-Ru-O/Ru MULTILAYER-ELECTRODES PREPARED BY MOCVD. Integrated Ferroelectrics, 2006, 81, 249-260.	0.3	3
479	Horizontal growth of epitaxial (100) Î²-FeSi2 templates by metalâ€“organic chemical vapor deposition. Journal of Crystal Growth, 2006, 287, 694-697.	0.7	3
480	MOCVD growth of epitaxial pyrochlore Bi2Ti2O7 thin film. Journal of the European Ceramic Society, 2006, 26, 2155-2159.	2.8	3
481	PROPERTIES OF A NOVEL BISMUTH PERCURSOR FOR MOCVD. Integrated Ferroelectrics, 2006, 84, 197-202.	0.3	3
482	Ruthenium and Ruthenium Oxide Films Deposition by MOCVD Using Ru(DMPD)2. ECS Transactions, 2006, 1, 139-144.	0.3	3
483	INTRINSIC PROPERTIES OF (100)/(001)-ORIENTED EPITAXIAL PZT THIN FILMS GROWN ON (100)SI AND (100)SrTiO3 SUBSTRATES. Integrated Ferroelectrics, 2006, 78, 223-232.	0.3	3
484	Effect of source materials on film thickness and compositional uniformity of MOCVD-P(Zr,Ti)O3 films. Surface and Coatings Technology, 2007, 201, 9279-9284.	2.2	3
485	Epitaxial growth of (100) Fe3Si thin films on insulating substrates. Journal of Crystal Growth, 2008, 310, 1703-1707.	0.7	3
486	Single domain epitaxial growth of yttria-stabilized zirconia on Si(111) substrate. Ceramics International, 2008, 34, 1047-1050.	2.3	3

#	Article	IF	Citations
487	Supercell Structure on Continuous Growth of Bi₂Sr₂Ca₁Cu₂O_x Film. Japanese Journal of Applied Physics, 2008, 47, 5602.	0.8	3
488	Effect of Incubation Time on Deposition Behavior of Ruthenium Films by MOCVD Using (2,4-Dimethylpentadienyl)(Ethylcyclopentadienyl)Ruthenium. Key Engineering Materials, 0, 421-422, 87-90.	0.4	3
489	Electric-Field-Induced Transverse Displacement in Pt/Pb(Zr,Ti)O3Film/Pt/Si Structure. Japanese Journal of Applied Physics, 2009, 48, 09KA04.	0.8	3
490	Low-Temperature Preparation of (111)-oriented Pb(Zr,Ti)O3Films Using Lattice-Matched (111)SrRuO3/Pt Bottom Electrode by Metalâ€“Organic Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2009, 48, 04C067.	0.8	3
491	Orientation controlled deposition of Pb(Zr,Ti)O3 films using a micron-size patterned SrRuO3 buffer layer. Journal of Materials Science, 2009, 44, 5339-5344.	1.7	3
492	Large Lattice Misfit on Epitaxial Thin Film: Coincidence Site Lattice Expanded on Polar Coordinate System. Japanese Journal of Applied Physics, 2010, 49, 08JE02.	0.8	3
493	A new SrBi₄Ti₄O₁₅/CaBi₄Ti₄O₁₅ thin-film capacitor for excellent electric stability. IEEE Transactions on Ultrasonics, Ferroelectrics, and Frequency Control, 2012, 59, 1888-1893.	1.7	3
494	Preparation and Characterization of Ba(Zr$_{x}$Ti$_{1-x}$)O$_{3}$ Thin Films Using Reactive Sputtering Method. Japanese Journal of Applied Physics, 2012, 51, 09LA01.	0.8	3
495	Crystal Structure Change with Applied Electric Field for (100)/(001)-oriented Polycrystalline Lead Zirconate Titanate Films. Materials Research Society Symposia Proceedings, 2013, 1507, 1.	0.1	3
496	Crystal orientation dependency of ferroelectric property in rhombohedral Pb(Zr,Ti)O3films. Japanese Journal of Applied Physics, 2014, 53, 04ED06.	0.8	3
497	Low Temperature Preparation of KNbO₃Films by Hydrothermal Method and Their Characterization. Materials Research Society Symposia Proceedings, 2014, 1659, 49-54.	0.1	3
498	Intermediate-temperature operation of solid oxide fuel cells (IT-SOFCs) with thin film proton conductive electrolyte. Journal of Physics: Conference Series, 2015, 660, 012057.	0.3	3
499	Structural characterization of epitaxial Mg₂Si films grown on MgO and MgO-buffered Al₂O₃substrates. Japanese Journal of Applied Physics, 2015, 54, 07JC01.	0.8	3
500	Growth and evaluation of epitaxial BaTiO₃thin films of less than 100 nm thickness by metalâ€“organic chemical vapor deposition. Japanese Journal of Applied Physics, 2015, 54, 035501.	0.8	3
501	Orientation and film thickness dependencies of (100)- and (111)-oriented epitaxial Pb(Mg1/3Nb2/3)O3 films grown by metal organic chemical vapor deposition. Journal of Materiomics, 2015, 1, 188-195.	2.8	3
502	Fabrication of Tetragonal Pb(Zr,Ti)O₃Nanorods by Focused Ion Beam and Characterization of the Domain Structure. IEEE Transactions on Ultrasonics, Ferroelectrics, and Frequency Control, 2016, 63, 1642-1646.	1.7	3
503	Electric-field-induced lattice distortion in epitaxial BiFeO3 thin films as determined by in situ time-resolved x-ray diffraction. Applied Physics Letters, 2017, 111, .	1.5	3
504	Fabrication and characterization of {110}-oriented Pb(Zr,Ti)O₃thin films on Pt/SiO₂/Si substrates using PdO//Pd buffer layer. Japanese Journal of Applied Physics, 2017, 56, 10PF09.	0.8	3

#	Article	IF	Citations
505	Orientation change with substrate type and composition in (100)/(001)-oriented epitaxial tetragonal Pb(Zr_xTi_{1−}_x)O₃ films. Journal of the Ceramic Society of Japan, 2017, 125, 458-462.	0.5	3
506	Ferroelastic domain motion by pulsed electric field in <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mrow><mml:mo>(</mml:mo><mml:mn>111</mml:mn><mm rhombohedral epitaxial <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi>Pb</mml:mi><mml:mrow><. Physical Review B, 2019, 100, .	1.1	3
507	Impact of stress on the crystal structural nonuniformity along the film thickness direction by microfabrication of Pb(Zr,Ti)O₃ islands with morphotropic phase boundary composition. Journal of the Ceramic Society of Japan, 2019, 127, 123-126.	0.5	3
508	Preparation of CaMgSi and Ca7Mg7.25Si14 single phase films and their thermoelectric properties. MRS Advances, 2019, 4, 1503-1508.	0.5	3
509	Epitaxial Growth of Doped HfO2 Ferroelectric Materials. , 2019, , 173-192.		3
510	Enhanced intrinsic piezoelectric response in (001)-epitaxial single c-domain Pb(Zr,Ti)O3 nanorods. Applied Physics Letters, 2020, 117, .	1.5	3
511	Site Engineering Concept of Ferroelectric Thin Films. Hyomen Kagaku, 2005, 26, 215-219.	0.0	3
512	Comparison of Ferroelectric and Insulating Properties of Mn-Doped BiFeO3Films Formed on Pt, SrRuO3/Pt, and LaNiO3/Pt Bottom Electrodes by Radio-Frequency Sputtering. Japanese Journal of Applied Physics, 2011, 50, 051501.	0.8	3
513	Film Thickness Dependence of Crystal Structure in 100-Oriented Epitaxial Pb(Zr0.65Ti0.35)O3Films Grown on Single-Crystal Substrates with Different Thermal Expansion Coefficients. Japanese Journal of Applied Physics, 2012, 51, 09LA14.	0.8	3
514	Composition dependencies of crystal structure and electrical properties of epitaxial tetragonal (Bi,) Tj ETQq0 0 0 rgBT /Overlock 10 Tf 50 depositions. Journal of Applied Physics, 2021, 130, .	1.1	3
515	Long-Range Lattice Matching between (100)/(010) Bismuth-Layered Perovskite Structure and (101) Rutile Structure. Materials Research Society Symposia Proceedings, 2002, 748, 1.	0.1	2
516	Growth of epitaxial tetragonal Pb(Zr,Ti)O₃thin films with 100% polar-axis-orientation and their electrical properties. Materials Research Society Symposia Proceedings, 2003, 784, 621.	0.1	2
517	Film Thickness Dependence of Electrical Properties for Pb(Zr,Ti)O 3 Thin Films Prepared on (111)Ir/TiO 2 /SiO 2 /Si and (111)Pt/TiO 2 /SiO 2 /Si Substrates by Pulsed-Metalorganic Chemical Vapor Deposition. Integrated Ferroelectrics, 2003, 59, 1421-1428.	0.3	2
518	THERMAL STABILITY OF EPITAXIAL SrRuO3 BOTTOM ELECTRODES AND THEIR CONTRIBUTION TO THE CHARACTERISTICS OF (Ba0.5Sr0.5)TiO3 FILMS GROWN ON THEM. Integrated Ferroelectrics, 2005, 77, 3-11.	0.3	2
519	A NEW METHOD TO CHARACTERIZE A RELATIVE VOLUME TO THE c-DOMAIN IN PZT FILMS BASED ON RAMAN SPECTRA. Integrated Ferroelectrics, 2006, 78, 281-287.	0.3	2
520	Strong Dependence on Thickness of Room-Temperature Dielectric Constant of (100)-Oriented Pb(Mg1/3Nb2/3)O3Epitaxial Films Grown by Metal Organic Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2006, 45, L1074-L1076.	0.8	2
521	TRIAL FOR MAKING THREE DIMENSIONAL PZT CAPACITOR FOR HIGH DENSITY FERROELECTRIC RANDOM ACCESS MEMORY. Integrated Ferroelectrics, 2006, 81, 219-226.	0.3	2
522	Single-phase Pb(Zn1/3Nb2/3)O3 thin films grown by metalorganic chemical vapor deposition: Effects of growth sequence and substrates. Journal of Crystal Growth, 2007, 298, 495-499.	0.7	2

#	Article	IF	Citations
523	Oxygen Content and Magnetic Properties of SrRuO$_{3 - delta}$ Thin Films. IEEE Transactions on Magnetics, 2007, 43, 3073-3075.	1.2	2
524	Structural modulation in bismuth cuprate superconducting film with continuous epitaxial growth. Journal of Crystal Growth, 2008, 310, 1713-1717.	0.7	2
525	IN-SITU OBSERVATION OF STRAIN ACCUMULATION AND RELAXATION IN PbTiO3 FILM DURING THERMAL PROCESS USING RAMAN SPECTROSCOPY. Integrated Ferroelectrics, 2008, 99, 23-30.	0.3	2
526	Preparation of (111)-Oriented SrRuO3/Pt Electrodes for Pb(Zr,Ti)O3-Based Ferroelectric Capacitors: Grain Size and Roughness Impact. Japanese Journal of Applied Physics, 2008, 47, 1003-1007.	0.8	2
527	Polarized Raman Study for Epitaxial PZT Thick Film with the Mixture Orientation of (100)/(001). Key Engineering Materials, 0, 421-422, 99-102.	0.4	2
528	Geometric Phase Analysis of Nano-Scale Strain Fields Around 90Â° Domains in PbTiO3/SrTiO3 Epitaxial Thin Film. Materials Research Society Symposia Proceedings, 2009, 1199, 12.	0.1	2
529	Fabrication of conductive oxide polycrystalline BaPbO3 films by chemical solution deposition and their electrical resistivity. Journal of Electroceramics, 2009, 22, 78-81.	0.8	2
530	Dielectric Properties of Highly (001)-Plane Oriented SrBi₄Ti₄O₁₅ Thin Films. Key Engineering Materials, 2010, 445, 131-134.	0.4	2
531	Comparison of Ferroelectric and Insulating Properties of Mn-Doped BiFeO3Films Formed on Pt, SrRuO3/Pt, and LaNiO3/Pt Bottom Electrodes by Radio-Frequency Sputtering. Japanese Journal of Applied Physics, 2011, 50, 051501.	0.8	2
532	Effects of A-Site Occupancy of Bismuth Ions on the Dielectric Tunable Properties of Pyrochlore Bismuth Zinc Niobate Films. Japanese Journal of Applied Physics, 2012, 51, 09LA10.	0.8	2
533	Anisotropic electrical properties in bismuth layer structured dielectrics with natural super lattice structure. Applied Physics Letters, 2012, 101, .	1.5	2
534	1.54Î¼m luminescence of Î²-FeSi2 grown on Au-coated Si substrates. Materials Research Society Symposia Proceedings, 2012, 1396, .	0.1	2
535	Preparation and Characterization of BaTiO₃ Thin Films Using Reactive Sputtering Method with Metal Target. Integrated Ferroelectrics, 2012, 133, 42-48.	0.3	2
536	Strain-Stable Nonlinear Dielectric Responses in Pyrochlore Bismuth Zinc Niobate Thin Films. Japanese Journal of Applied Physics, 2013, 52, 09KA13.	0.8	2
537	Control of Volume Fraction of Non-180Â° Domains by Thermal Strain in Epitaxial Rhombohedral Pb(Zr,) Tj ETQq1 1 0.784314 rgBT /Ov	0.1	2
538	Characterizations of epitaxial Bi(Mg_{1/2}Ti_{1/2})O₃â€“Bi(Zn_{1/2}Ti_{1/2})O₃ solid solution films grown by pulsed laser deposition. Japanese Journal of Applied Physics, 2014, 53, 05FE06.	0.8	2
539	Structural and tunable characteristics of Ba(Zr x Ti1â^'x)O3 films prepared by RF-magnetron sputtering using a metal target. Journal of the Korean Physical Society, 2014, 65, 275-280.	0.3	2
540	Dielectric property of (001) one-axis oriented CaBi₄Ti₄O₁₅-based thin films and their temperature dependence. Journal of the Ceramic Society of Japan, 2014, 122, 477-482.	0.5	2

#	Article	IF	Citations
541	Chemical and structural effects on ionic conductivity at columnar grain boundaries in yttria-stabilized zirconia thin films. Journal of the Ceramic Society of Japan, 2014, 122, 430-435.	0.5	2
542	Activation of piezoelectric property of PZT thin films by pulse poling. Journal of Physics: Conference Series, 2014, 557, 012130.	0.3	2
543	Fabrication of tetragonal Pb(Zr,Ti)O<inf>3</inf> nanorods by focused ion beam and characterization of the domain structure. , 2015, , .		2
544	Chemical Fluid Deposition of Hf-Zr-O-based Thin Films using Supercritical Carbon Dioxide Fluid. Materials Research Society Symposia Proceedings, 2015, 1729, 99-104.	0.1	2
545	Fabrication and characterization of (111)-epitaxial Pb(Zr0.35Ti0.65)O3/Pb(Zr0.65Ti0.35)O3artificial superlattice thin films. Japanese Journal of Applied Physics, 2016, 55, 10TA20.	0.8	2
546	Dielectric properties of BaTiO₃–Bi(Mg_{1/2}Ti_{1/2})O₃ films with preferential crystal orientation. Journal of the Ceramic Society of Japan, 2016, 124, 648-652.		
547	The microstructural evolution in high sodium epitaxial sodium potassium niobate films deposited by low-temperature hydro-thermal method. Journal of Materials Science, 2017, 52, 6950-6961.	1.7	2
548	Synthesis and Photocatalytic Properties of Iron Disilicide/SiC Composite Powder. MRS Advances, 2017, 2, 471-476.	0.5	2
549	Effect of microstructures on electrical conduction properties of Î²-FeSi2 epitaxial films. Journal of Crystal Growth, 2017, 468, 744-748.	0.7	2
550	Inverse-magnetostriction-induced switching current reduction of STT-MTJs and its application for low-voltage MRAM. Solid-State Electronics, 2017, 128, 194-199.	0.8	2
551	Effect of substrate type and temperature on the growth of thin Ru films by metal organic chemical vapor deposition. Materials Science in Semiconductor Processing, 2017, 70, 73-77.	1.9	2
552	Enhancement of photoluminescence from iron disilicide on Si(111) substrates with Au layers by controlling microstructures. Japanese Journal of Applied Physics, 2017, 56, 06HE03.	0.8	2
553	Piezoelectronic transistor for low-voltage high-speed integrated electronics. , 2017, , .		2
554	Epitaxial growth of perovskite-type oxide thin film on (111)SrTiO₃ substrate using (101)PdO as a buffer layer. Japanese Journal of Applied Physics, 2018, 57, 11UF04.	0.8	2
555	Time response demonstration of in situ lattice deformation under an applied electric field by synchrotron-based time-resolved X-ray diffraction in polar-axis-oriented epitaxial Pb(Zr,Ti)O3 film. Japanese Journal of Applied Physics, 2018, 57, 0902B8.	0.8	2
556	Electric field-induced change in the crystal structure of MOCVD-Pb(Zr,Ti)O3 films near the phase boundary. Japanese Journal of Applied Physics, 2019, 58, SLLB07.	0.8	2
557	Structural Origin of Temperature-Dependent Ferroelectricity. , 2019, , 193-216.		2
558	Growth of epitaxial bismuth ruthenate pyrochlore films on yttria-stabilized zirconia (YSZ) and YSZ-buffered Si substrates by metalâ€“organic chemical vapor deposition. Thin Solid Films, 2019, 669, 471-474.	0.8	2

#	Article	IF	Citations
559	Tensor factorization for elucidating mechanisms of piezoresponse relaxation via dynamic Piezoresponse Force Spectroscopy. Npj Computational Materials, 2020, 6, .	3.5	2
560	Epitaxial Crystal Growth of Bismuth Silicate Driven by Fluorite-like Layers. Crystal Growth and Design, 2020, 20, 7163-7169.	1.4	2
561	NiSi2 as a bottom electrode for enhanced endurance of ferroelectric Y-doped HfO2 thin films. Japanese Journal of Applied Physics, 2020, 59, SGGB06.	0.8	2
562	Growth of 0.1(Bi,Na)TiO₃â€“0.9BaTiO₃ epitaxial films by pulsed laser deposition and their electric properties. Journal of the Ceramic Society of Japan, 2021, 129, 337-342.	0.5	2
563	Domain structure transition in compressively strained (100)/(001) epitaxial tetragonal PZT film. Journal of Applied Physics, 2021, 129, 024101.	1.1	2
564	Interfacial dislocations in (111) oriented (Ba0.7Sr0.3)TiO3films on SrTiO3single crystal. Applied Physics Letters, 2015, 107, 141605.	1.5	2
565	Low Temperature Operation of Solid Oxide Fuel Cells (SOFCs) with Proton Conductive Electrolyte Deposited on Pd Foil Substrates. Science of Advanced Materials, 2017, 9, 1797-1800.	0.1	2
566	Tin oxide thin films deposited by spray CVD using ethanol solution of tin (II) chloride. Transactions of the Materials Research Society of Japan, 2008, 33, 1363-1366.	0.2	2
567	Effects of A-Site Occupancy of Bismuth Ions on the Dielectric Tunable Properties of Pyrochlore Bismuth Zinc Niobate Films. Japanese Journal of Applied Physics, 2012, 51, 09LA10.	0.8	2
568	Polarization switching behavior of one-axis-oriented lead zirconate titanate films fabricated on metal oxide nanosheet layer. Japanese Journal of Applied Physics, 2017, 56, 10PF10.	0.8	2
569	Domain structures induced by tensile thermal strain in epitaxial PbTiO3 films on silicon substrates. Journal of Applied Physics, 2022, 131, 035301.	1.1	2
570	Noâ€Heating Deposition of 1â€¼mâ€Thick Yâ€Doped HfO₂ Ferroelectric Films with Good Ferroelectric and Piezoelectric Properties by Radio Frequency Magnetron Sputtering Method. Physica Status Solidi - Rapid Research Letters, 2022, 16, .	1.2	2
571	Deposition and evaluation of Ta₂O₅ piezoelectric thin film on Pt crystal film. Japanese Journal of Applied Physics, 2022, 61, SG1076.	0.8	2
572	Film thickness dependence of ferroelectric properties in polar-axis-oriented epitaxial tetragonal (Bi,K)TiO₃ films prepared by hydrothermal method. AIP Advances, 2022, 12, 035241.	0.6	2
573	Preparation of orthorhombic Y-doped TaON film. Journal of the Ceramic Society of Japan, 2022, 130, 432-435.	0.5	2
574	Preparation and deposition mechanism of tantalum nitride films by CVD.. Kagaku Kogaku Ronbunshu, 1990, 16, 430-437.	0.1	1
575	Grain Boundary Structure of Bi₂O₃-Diffused BaTiO₃ BL Capacitor. Journal of the Ceramic Society of Japan, 1992, 100, 1266-1270.	1.3	1
576	Preparation of FeNx-TiN films by CVD. Journal of Materials Science, 1993, 28, 994-998.	1.7	1

#	Article	IF	Citations
577	Microstructure of Iron Nitride-Titanium Nitride Films Prepared by CVD. Journal of the Ceramic Society of Japan, 1993, 101, 733-736.	1.3	1
578	Preparation of PbTiO3 thin film by laser-assisted cvd and its electrical properties. Integrated Ferroelectrics, 1998, 20, 159-172.	0.3	1
579	Diffusion of Bi into ZnO Film Prepared by CVD and Its I-V Characteristics. Key Engineering Materials, 1998, 157-158, 175-180.	0.4	1
580	Effects of growth conditions and RF plasma on crystalline and electrical properties of SrBi2Ta2O9 thin films grown by liquid delivery MOCVD using a double alcoholate. Integrated Ferroelectrics, 1999, 26, 109-117.	0.3	1
581	Preparation and Characterization of a- and b-Axis-Oriented Epitaxially Grown Bi4Ti3O12-Based Thin Films on Rutile-Type Oxides. Materials Research Society Symposia Proceedings, 2001, 688, 1.	0.1	1
582	Effect of composition of MOCVD-SrRuO3top electrode of (Pb, La)(Zr, Ti)O3capacitor on H2degradation. Ferroelectrics, 2001, 260, 57-62.	0.3	1
583	Conduction Mechanism of La-, Nb-Doped BaTiO₃ Thin Films by Doping MOCVD. Key Engineering Materials, 2001, 216, 87-92.	0.4	1
584	Ferroelectricity of Epitaxial and Polycrystalline PZT Films Prepared by Pulsed-MOCVD. Key Engineering Materials, 2002, 228-229, 69-74.	0.4	1
585	Effect of Thermal Strain on Domain Fraction in a-/b-axis-oriented Epitaxial Bi4Ti3O12 Films. Materials Research Society Symposia Proceedings, 2003, 784, 421.	0.1	1
586	Property Improvement of Mocvd-Pzt Films Deposited Below 400 Â°C. Materials Research Society Symposia Proceedings, 2003, 784, 431.	0.1	1
587	Film Thickness Dependence of Electrical Properties for Pb(Zr,Ti)O3 Thin Films Prepared on (111)Ir/TiO2/SiO2/Si and (111)Pt/TiO2/SiO2/Si Substrates by Pulsed-Metalorganic Chemical Vapor Deposition. Integrated Ferroelectrics, 2003, 59, 1421-1428.	0.3	1
588	Advanced X-ray Analysis of Ferroelectrics. , 2005, , 119-136.		1
589	Preparation and Structural Analysis of Micro-patterned Pb(Zr,Ti)O3Film by Metalorganic Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2006, 45, 5102-5106.	0.8	1
590	Fatigue Properties of Epitaxial Pb(Zr0.35Ti0.65)O3Films with Various Volume Fractions of 90Â° Domains Grown on (100)cSrRuO3/(100)SrTiO3Substrates. Japanese Journal of Applied Physics, 2006, 45, 6382-6384.	0.8	1
591	Formation of Stoichiometric SrRuO[sub 3] Electrodes for PZT Capacitors by Pulsed-MOCVD. Electrochemical and Solid-State Letters, 2006, 9, C164.	2.2	1
592	BOTTOM ELECTRODES DEPENDENCE OF FERROELECTRIC PROPERTIES IN EPITAXIAL BiFeO3/SrRuO3/SrTiO3 STRUCTURES. Integrated Ferroelectrics, 2007, 87, 42-49.	0.3	1
593	Characterization of zinc-modified lithium tantalate thin films fabricated by chemical solution deposition method. Journal of Sol-Gel Science and Technology, 2007, 42, 265-269.	1.1	1
594	Growth of Epitaxial Potassium Niobate Film on (100)SrRuO3/(100)SrTiO3 by Hydrothermal Method and their Electromechanical Properties. Materials Research Society Symposia Proceedings, 2008, 1139, 1.	0.1	1

#	Article	IF	Citations
595	Ligand Structure Effect on A Divalent Ruthenium Precursor for MOCVD. Materials Research Society Symposia Proceedings, 2009, 1155, 1.	0.1	1
596	Determination Factors of Strain-relaxed Complex Domain Structure observed in Thick Epitaxial pb(Zr,Ti)O3Films. Materials Research Society Symposia Proceedings, 2009, 1199, 142.	0.1	1
597	Influence of Pb and La contents on the lattice configuration of La-substituted Pb(Zr,Ti)O3 films fabricated by CSD method. IEEE Transactions on Ultrasonics, Ferroelectrics, and Frequency Control, 2009, 56, 687-692.	1.7	1
598	Synthesis of Mica Thin Film by Pulsed Laser Deposition. Applied Physics Express, 2011, 4, 055502.	1.1	1
599	Fabrication and Evaluation of Mn-Substituted Ba(Cu1/3Nb2/3)O3Ceramics. IOP Conference Series: Materials Science and Engineering, 2011, 18, 092038.	0.3	1
600	Epitaxial growth of (100)-oriented Î²-FeSi2 film on 3Cî—¸SiC(100) plane. Journal of Crystal Growth, 2011, 316, 10-14.	0.7	1
601	Dielectric Property of Silicate-Doped CaBi$_{4}$Ti$_{4}$O$_{15}$ Thin Films. Japanese Journal of Applied Physics, 2012, 51, 09LA16.	0.8	1
602	Effect of point defects on lattice constant in MgO thin film deposited on silicon(0 0 1) substrate. EPJ Applied Physics, 2012, 58, 10302.	0.3	1
603	Stacking faults in an epitaxially grown PbTiO3 thick film and their size distribution. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2012, 177, 528-531.	1.7	1
604	Identification of the Occupation Site of Dy- or Y-Substituted PZT Films and the Correlation Between Occupation Site and Ferroelectric Property. Integrated Ferroelectrics, 2013, 141, 1-8.	0.3	1
605	One-Axis-Oriented Crystal Growth of Lead Zirconate Titanate Thin Films on Metal Substrates Using Perovskite-Type Oxide Nanosheet Layer. Key Engineering Materials, 2013, 582, 15-18.	0.4	1
606	Epitaxial growth of (010)-oriented Î²-FeSi2 film on Si(110) substrate. Materials Research Society Symposia Proceedings, 2013, 1493, 189-194.	0.1	1
607	Preparation of Bismuth Based Perovskite Oxides and their Electric Properties. Key Engineering Materials, 2013, 582, 71-75.	0.4	1
608	Direct Observation of Atomic Arrangement around 90Â° Domain Wall in Lead Titanate Thin Films.. Materials Research Society Symposia Proceedings, 2013, 1515, 1.	0.1	1
609	Squareness Control in Polarizationâ€“Electric Field Hysteresis Curves in Rhombohedral Pb(Zr,Ti)O3Films. Japanese Journal of Applied Physics, 2013, 52, 04CD09.	0.8	1
610	Nano-Structure around 90Â° Domain Wall and Elastic Interaction with Misfit Dislocation in PbTiO₃ Thin Film. Key Engineering Materials, 2013, 566, 167-170.	0.4	1
611	Bi4Ti3O12Nanowall Growth Driven by Anisotropic Growth Rate and Size Control. Japanese Journal of Applied Physics, 2013, 52, 09KA09.	0.8	1
612	Epitaxial growth of luminescent Î²-FeSi2on modified Si(111) surface by silver. , 2015, , .		1

#	Article	IF	Citations
613	Low temperature MOCVD of Ta₂O₅ dielectric thin films from Ta[NC(CH₃)₃][OC(CH₃)₃]₃ and O₂. Journal of the Ceramic Society of Japan, 2016, 124, 510-514.	0.5	1
614	Composition dependences of crystal structure and electrical properties of epitaxial Pb(Zr,Ti)O3films grown on Si and SrTiO3substrates. Japanese Journal of Applied Physics, 2016, 55, 10TA08.	0.8	1
615	Effects of substrate surface composition and deposition temperature on deposition of flat and continuous Ru thin films. Journal of the Ceramic Society of Japan, 2016, 124, 694-696.	0.5	1
616	Epitaxial growth and photoluminescence properties of Î²-FeSi₂grains using liquid phase obtained by Au-Si eutectic reaction. Proceedings of SPIE, 2016, , .	0.8	1
617	On the Use of 31Mg for Î²-Detected NMR Studies of Solids. , 2018, , .		1
618	Solid-solution thin films of ternary BaTiO3â€“Bi(Mg1/2Ti1/2)O3â€“BiFeO3 system epitaxially grown on SrRuO3//SrTiO3 substrates via chemical solution process. Japanese Journal of Applied Physics, 2018, 57, 0902B5.	0.8	1
619	Epitaxial growth of (Bi,K)TiO3-Bi(Mg,Ti)O3 (001) films and their ferroelectric and piezoelectric properties. Japanese Journal of Applied Physics, 2019, 58, SLLB13.	0.8	1
620	Composition Dependence of Crystal Structures and Electrical Properties of Ca-Mg-Si Films Prepared by Sputtering. Journal of Electronic Materials, 2020, 49, 7509-7517.	1.0	1
621	Preparation of iridium metal films by spray chemical vapor deposition. MRS Advances, 2020, 5, 1681-1685.	0.5	1
622	Electricâ€Fieldâ€Induced Ferroelectricity in 5%Yâ€doped Hf_{0.5}Zr_{0.5}O₂: Transformation from the Paraelectric Tetragonal Phase to the Ferroelectric Orthorhombic Phase. Physica Status Solidi - Rapid Research Letters, 2021, 15, 2170023.	1.2	1
623	High-precision local Câ€“V mapping for ferroelectrics using principal component analysis. Japanese Journal of Applied Physics, 2021, 60, SFFB09.	0.8	1
624	Influence of Internal Strains of (110)-One-Axis-Oriented (Ba0.5Sr0.5)TiO3 (BST) Thin Films on Their Dielectric Behaviors. Science of Advanced Materials, 2017, 9, 1806-1809.	0.1	1
625	Evaluation of Chemical Stability in Perovskite-Type Proton-Conductive Oxide Thin-Films. Science of Advanced Materials, 2018, 10, 8-11.	0.1	1
626	Nanostructural Characterization of Surfaces, Interfaces, and Thinfilms using X-ray Reciprocal-Lattice Space Imaging. Nihon Kessho Gakkaishi, 2007, 49, 292-299.	0.0	1
627	Preparation of InP Nanoparticles by Laser Ablation in Liquid. The Review of Laser Engineering, 2012, 40, 117.	0.0	1
628	Room-temperature photoluminescence spectrum from Î²-FeSi2 films. , 2018, , .		1
629	Lower-temperature processing of potassium niobate films by microwave-assisted hydrothermal deposition technique. Journal of the Ceramic Society of Japan, 2022, 130, 123-130.	0.5	1
630	Evaluation of bulk and surface acoustic waves propagation properties of (K,Na)NbO₃ films deposited by hydrothermal synthesis or RF magnetron sputtering methods. Japanese Journal of Applied Physics, 2022, 61, SG1077.	0.8	1

#	Article	IF	Citations
631	Preparations and Characterizations of Epitaxial SrBi2Ta2O9 Thin Films. Materials Research Society Symposia Proceedings, 2000, 655, 48.	0.1	0
632	Property Improvement of PLZT Capacitor Using CaRuO3 Top Electrode. Materials Research Society Symposia Proceedings, 2000, 655, 335.	0.1	0
633	Hetero-epitaxial Growth of (1, 0, m+1) One Axis-oriented Bismuth Layered Structured Ferroelectrics Thin Films Directly Crystallized by MOCVD. Materials Research Society Symposia Proceedings, 2001, 688, 1.	0.1	0
634	A new combinatorial process to fabricate PZT thin film from chemical sauces. , 0, , .		0
635	Growth of Epitaxial Site-Engineered Bi4Ti3O12-Basded Thin Films by Mocvdand Their Characterization. Materials Research Society Symposia Proceedings, 2002, 748, 1.	0.1	0
636	Characteristic Comparison Of Epitaxial PZT And PMN-PT Films Grown On (100)cSrRuO3//(100)SrTiO3 Substrates By Metalorganic Chemical Vapor Deposition. Materials Research Society Symposia Proceedings, 2005, 902, 1.	0.1	0
637	Dominant Factor of Squareness in P-E Hsyteresis Loops of MOCVD-PZT Films. Materials Research Society Symposia Proceedings, 2005, 902, 1.	0.1	0
638	Dielectric Property Controls Using Crystal Structure Anisotropy In Bismuth Layer-Structured Dielectrics. Materials Research Society Symposia Proceedings, 2005, 902, 1.	0.1	0
639	Electrical Properties of Perovskite-Based Ferroelectric Thin Films Modified Using Rare-Earth Elements. Key Engineering Materials, 2006, 320, 49-52.	0.4	0
640	X-ray Analysis of Strain Relaxed Domain Structure in (100)/(001)-oriented epitaxial PbTiO3 thick films grown on (100)SrTiO3 substrates. Materials Research Society Symposia Proceedings, 2007, 1034, 146.	0.1	0
641	Analysis of domain structure of epitaxial Pb(Zr, Ti)O<inf>3</inf> films applied electric field by 2D-XRD. Applications of Ferroelectrics, IEEE International Symposium on, 2007, , .	0.0	0
642	Structural and ferroelectric properties of BiFeO<inf>3</inf>-BiCoO<inf>3</inf> solid solution films. Applications of Ferroelectrics, IEEE International Symposium on, 2007, , .	0.0	0
643	Characteristic Comparison of Epitaxial PZT and PMN-PT Films Grown On (100)<inf>c</inf>SrRuO<inf>3</inf>//(100)SrTiO<inf>3</inf> Substrates By Metalorganic Chemical Vapor Deposition. Applications of Ferroelectrics, IEEE International Symposium on, 2007, , .	0.0	0
644	Effect of the Strain from the Substrate on Tunability of(100) One-axis Oriented (Ba<inf>0.5</inf>Sr<inf>0.5</inf>)TiO<inf>3</inf> Thin Films. Applications of Ferroelectrics, IEEE International Symposium on, 2007, , .	0.0	0
645	Substrate effects on the novel domain structure of (100)/(001)-oriented epitaxial PbTiO3 thick films. Applications of Ferroelectrics, IEEE International Symposium on, 2007, , .	0.0	0
646	Structural analysis in (100)/(001)-oriented epitaxial lead titanate thick films grown by MOCVD for MEMS application. Applications of Ferroelectrics, IEEE International Symposium on, 2007, , .	0.0	0
647	Influence of Pb and La Contents on the Lattice Configuration of La-Substituted Pb(Zr<inf>0.65</inf>,) Tj ETQq1 1 0.784314 rgBT /Ov 2007, , .	0.0	0
648	Preparation and characterization of Bi-perovskite oxide films for piezo applications. Applications of Ferroelectrics, IEEE International Symposium on, 2007, , .	0.0	0

#	Article	IF	Citations
649	In situ gas-phase FTIR monitoring of liquid delivery MOCVD process for PZT film preparation. Chemical Engineering Journal, 2008, 135, 10-14.	6.6	0
650	Effect of the Annealing Temperature on Dielectric Properties of Bi_{1.5}Zn_{1.0}Nb_{1.5}O₇ Films Prepared by MOCVD. Key Engineering Materials, 0, 388, 175-178.	0.4	0
651	In-Plane Rotated Crystal Structure in Continuous Growth of Bismuth Cuprate Superconducting Film. Solid State Phenomena, 2008, 139, 53-58.	0.3	0
652	Temperature Dependency of Dielectric Properties in Epitaxially Grown SrBi₄Ti₄O₁₅ Films with Different Orientation. Key Engineering Materials, 0, 368-372, 1811-1813.	0.4	0
653	Effect of Strain on Supercell Structure of Bismuth Cuprate Superconducting Film. Japanese Journal of Applied Physics, 2008, 47, 664-666.	0.8	0
654	Solution-Based Fabrication of High-k Dielectrics Using Oxide Nanosheets. ECS Transactions, 2009, 25, 349-352.	0.3	0
655	One-axis Oriented CaBi4Ti4O15 and SrBi4Ti4O15 Films Prepared on Silicon Wafer by Chemical Solution Deposition Technique. Materials Research Society Symposia Proceedings, 2009, 1199, 54.	0.1	0
656	Investigation of Oxygen Vacancies in Micro-Patterned PZT Thin Films Using Raman Spectroscopy. Key Engineering Materials, 2009, 421-422, 135-138.	0.4	0
657	RF-sputtered BST film microwave tunable device on comparison between MgO(111) and (100) substrate. , 2009, , .		0
658	Process-dependent Coercive Fields in Undoped and Mn-doped BiFeO3 Films Formed on SrRuO3/Pt(111) Electrodes by rf Sputtering. Materials Research Society Symposia Proceedings, 2009, 1199, 137.	0.1	0
659	Self-assembled ferroelectric-dielectric nanocomposite films for tunable applications. IOP Conference Series: Materials Science and Engineering, 2010, 8, 012010.	0.3	0
660	In-situ observation of a MEMS-based Pb(Zr,Ti)O3 micro cantilever using micro-Raman spectroscopy. Journal of the Ceramic Society of Japan, 2010, 118, 644-647.	0.5	0
661	Growth of polar axis oriented tetragonal Pb(Zr,Ti)O3 films on CaF2 substrates with transparent (La0.07Sr0.93)SnO3. Journal of Crystal Growth, 2010, 312, 3127-3130.	0.7	0
662	Investigation of SrBi<inf>4</inf>Ti<inf>4</inf>O<inf>15</inf>/CaBi<inf>4</inf>Ti<inf>4</inf>O<inf>15</inf> thin film capacitor for excellent electric stability. , 2011, , .		0
663	TEM Observation on Ferroelectric Domain Structures of PbTiO₃ Epitaxial Films. Key Engineering Materials, 2011, 485, 179-182.	0.4	0
664	Rapid and high sensitive structure evaluation of ferroelectric films using micro-Raman spectroscopy:In-situobservation of stress accumulation and release in PbTiO3films during first cooling process. IOP Conference Series: Materials Science and Engineering, 2011, 18, 092002.	0.3	0
665	Intrinsic Characteristics of Bi(Zn1/2Ti1/2)O3- substituted Pb(Zr0.4Ti0.6)O3Thin Films. IOP Conference Series: Materials Science and Engineering, 2011, 18, 092008.	0.3	0
666	A New SrBi<inf>4</inf>Ti<inf>4</inf>O<inf>15</inf>/CaBi<inf>4</inf>Ti<inf>4</inf>O<inf>15</inf> thin film capacitor for excellent electric stability. , 2011, , .		0

#	Article	IF	Citations
667	Measurement of Piezoelectric Transverse and Longitudinal Displacement with Atomic Force Microscopy for PZT Thick Films. Materials Research Society Symposia Proceedings, 2011, 1318, 1.	0.1	0
668	Dielectric Properties of Bismuth Layer-Structured Oxide Thin Films with Preferential Crystal Orientation at High-Temperature. Key Engineering Materials, 0, 485, 191-194.	0.4	0
669	Investigation of Sputtering Damage in SrRuO$_{3}$ Films Prepared by Sputtering with Raman and X-ray Photoemission Spectroscopies. Japanese Journal of Applied Physics, 2012, 51, 09LA19.	0.8	0
670	Distribution of Crystal Structure in Epitaxial Pb(Zr_{0.42},Ti_{0.58})O₃ Film Grown on (111) _c SrRuO₃//(111)SrTiO₃ Substrate. Integrated Ferroelectrics, 2012, 133, 54-60.	0.3	0
671	Development of novel Pb, Li, Na and K-free piezoelectric materials for Si-based MEMS application. , 2012, , .		0
672	Temperature and Frequency Dependencies of Ferroelectric Properties in Rhombohedral Epitaxial Pb(Zr,Ti)O3 Films with Perfect (111) Orientations Grown on CaF2 Substrates.. Materials Research Society Symposia Proceedings, 2012, 1397, 65.	0.1	0
673	Noncontact probing method for estimation of ferroelectric properties of PbTiO₃-based films for microelectromechanical systems. Journal of Materials Research, 2012, 27, 1430-1435.	1.2	0
674	Enhanced perfomance of sensor/actuator integrated piezoelectric microcantilever by using tetragonal compositon PZT thin films. , 2013, , .		0
675	Analysis of Lattice Defects in an Epitaxial PbTiO₃ Thick Film by Transmission Electron Microscopy. Key Engineering Materials, 0, 566, 171-174.	0.4	0
676	Fabrication of BiFeO₃-Bi(Zn_{1/2}Ti_{1/2})O₃ Solid Solution Thin Films Using Perovskite-Type Oxide Interface Layer. Key Engineering Materials, 0, 566, 163-166.	0.4	0
677	Leakage current characteristics of new SrBi<inf>4</inf>Ti<inf>4</inf>O<inf>15</inf>/CaBi<inf>4</inf>Ti<inf>4</inf>O<inf thin-film capacitor with excellent electric stability. , 2013, , .		0
678	Structural and Electrical Properties of Ba(ZrxTi1-x)O3 Films Prepared by RF-magnetron Sputtering Using Metal Targets. Integrated Ferroelectrics, 2014, 157, 101-113.	0.3	0
679	In-situ Raman Spectroscopic Investigation of the Effect of Cooling Speed on Domain Formation in PbTiO3 Films. Integrated Ferroelectrics, 2014, 157, 39-46.	0.3	0
680	High power piezoelectric characteristics of KNbO<inf>3</inf> thick films by hydrothermal method. , 2015, , .		0
681	Inverse-magnetostriction-induced switching current reduction of STT-MTJs and its application for low-voltage MRAMs. , 2016, , .		0
682	Probing Oxygen Vacancies in BaTiO3 Powders and Single Crystals by Micro-Raman Scattering. Advanced Structured Materials, 2017, , 65-75.	0.3	0
683	Thickness and temperature dependences of dielectric properties of {111}-oriented epitaxial Pb(Mg_{1/3}Nb_{2/3})O₃ and 0.6Pb(Mg_{1/3}Nb_{2/3})O₃â€“0.4PbTiO₃ films. Japanese Journal of Applied Physics, 2018, 57, 0902BA.	0.8	0
684	Evaluation of strain components in PbTiO₃ thin films by micro-raman spectroscopy. Journal of the Ceramic Society of Japan, 2018, 126, 936-939.	0.5	0

#	Article	IF	Citations
685	Growth of (110)-one-axis-oriented perovskite-type oxide thin films with local epitaxy on (111)SrTiO3 single crystal substrates. Japanese Journal of Applied Physics, 2019, 58, SLLB01.	0.8	0
686	Kinetics of interfacial microstructural variation across insulator-thermoelectric semiconductor interface and its effects on thermoelectric properties of magnesium silicide thin films. Materialia, 2019, 7, 100375.	1.3	0
687	Modeling and Design of a New Piezoelectronic Transistor for Ultralow-Voltage High-Speed Integrated Circuits. IEEE Transactions on Electron Devices, 2020, 67, 3852-3860.	1.6	0
688	Fabrication and characterization of (CaxSr1-x)Si2 films prepared by co-sputtering method. MRS Advances, 2020, 5, 451-458.	0.5	0
689	Fabrication and characterization of ReO3-type dielectric films. Journal of Materials Chemistry C, 2020, 8, 4680-4684.	2.7	0
690	Local C-V Characterization for Ferroelectric Films. , 2021, , .		0
691	Size Effect of Ferroelectric and High Permittivity Thin Films. , 2006, , 99-134.		0
692	Observation of 1D and 2D nanostructures using the X-ray reciprocal-lattice space imaging method. Acta Crystallographica Section A: Foundations and Advances, 2008, 64, C548-C549.	0.3	0
693	Dielectric Property of Silicate-Doped CaBi₄Ti₄O₁₅Thin Films. Japanese Journal of Applied Physics, 2012, 51, 09LA16.	0.8	0
694	Investigation of Sputtering Damage in SrRuO3Films Prepared by Sputtering with Raman and X-ray Photoemission Spectroscopies. Japanese Journal of Applied Physics, 2012, 51, 09LA19.	0.8	0
695	Preparation of Bismuthï¼Based Perovskites with Non-integer A and B Site Valence and Their Properties. Transactions of the Materials Research Society of Japan, 2013, 38, 49-52.	0.2	0
696	Fabrication of (110)-one-axis-oriented perovskite-type oxide thin films and their application to buffer layer. Japanese Journal of Applied Physics, 2016, 55, 10TA19.	0.8	0
697	Hydrothermal Deposition of KNbO₃ Films on Metal Substrates having Three-Dimensional Structure. Funtai Oyobi Fummatsu Yakin/Journal of the Japan Society of Powder and Powder Metallurgy, 2018, 65, 673-677.	0.1	0
698	Ferroelectric property improvement of Pb(Zr/sub x/Ti/sub 1-x/)O/sub 3/ films by source gas pulse-introduced MOCVD. , 0, , .		0
699	Evaluation of BAW and SAW Properties of (K, Na)NbO3 Thin Films Deposited by RF Sputtering. , 2021, , .		0